



US010652058B2

(12) **United States Patent**
Muellner

(10) **Patent No.:** **US 10,652,058 B2**
(45) **Date of Patent:** ***May 12, 2020**

(54) **INTEGRATED CIRCUITS AND
TRANSPONDER CIRCUITRY WITH SHARED
MODULATION CAPACITOR FOR 3D
TRANSPONDER UPLINK MODULATION**

(56) **References Cited**

U.S. PATENT DOCUMENTS

5,347,280	A *	9/1994	Schuermann	G01S 13/758
				342/42
5,864,302	A	1/1999	Kokubu	
6,239,675	B1 *	5/2001	Flaxl	G06K 7/10316
				334/55
6,356,198	B1 *	3/2002	Wuidart	G06K 19/0723
				235/384

(71) Applicant: **TEXAS INSTRUMENTS
INCORPORATED**, Dallas, TX (US)

(72) Inventor: **Ernst Georg Muellner**, Munich (DE)

(73) Assignee: **TEXAS INSTRUMENTS
INCORPORATED**, Dallas, TX (US)

(Continued)

(*) Notice: Subject to any disclaimer, the term of this patent is extended or adjusted under 35 U.S.C. 154(b) by 0 days.

FOREIGN PATENT DOCUMENTS

RU	2461018	C2	8/2006
RU	2490776	C1	8/2013

(Continued)

This patent is subject to a terminal disclaimer.

OTHER PUBLICATIONS

(21) Appl. No.: **16/020,530**

International Search Report, PCT/US2018/021672, dated Jun. 7, 2018 (7 pages).

(22) Filed: **Jun. 27, 2018**

European Search Report dated Feb. 6, 2020.

(65) **Prior Publication Data**

US 2018/0316528 A1 Nov. 1, 2018

Primary Examiner — Syed Haider

(74) *Attorney, Agent, or Firm* — Brian D. Graham;
Charles A. Brill; Frank D. Cimino

Related U.S. Application Data

(63) Continuation of application No. 15/459,696, filed on Mar. 15, 2017, now Pat. No. 10,038,579.

(57) **ABSTRACT**

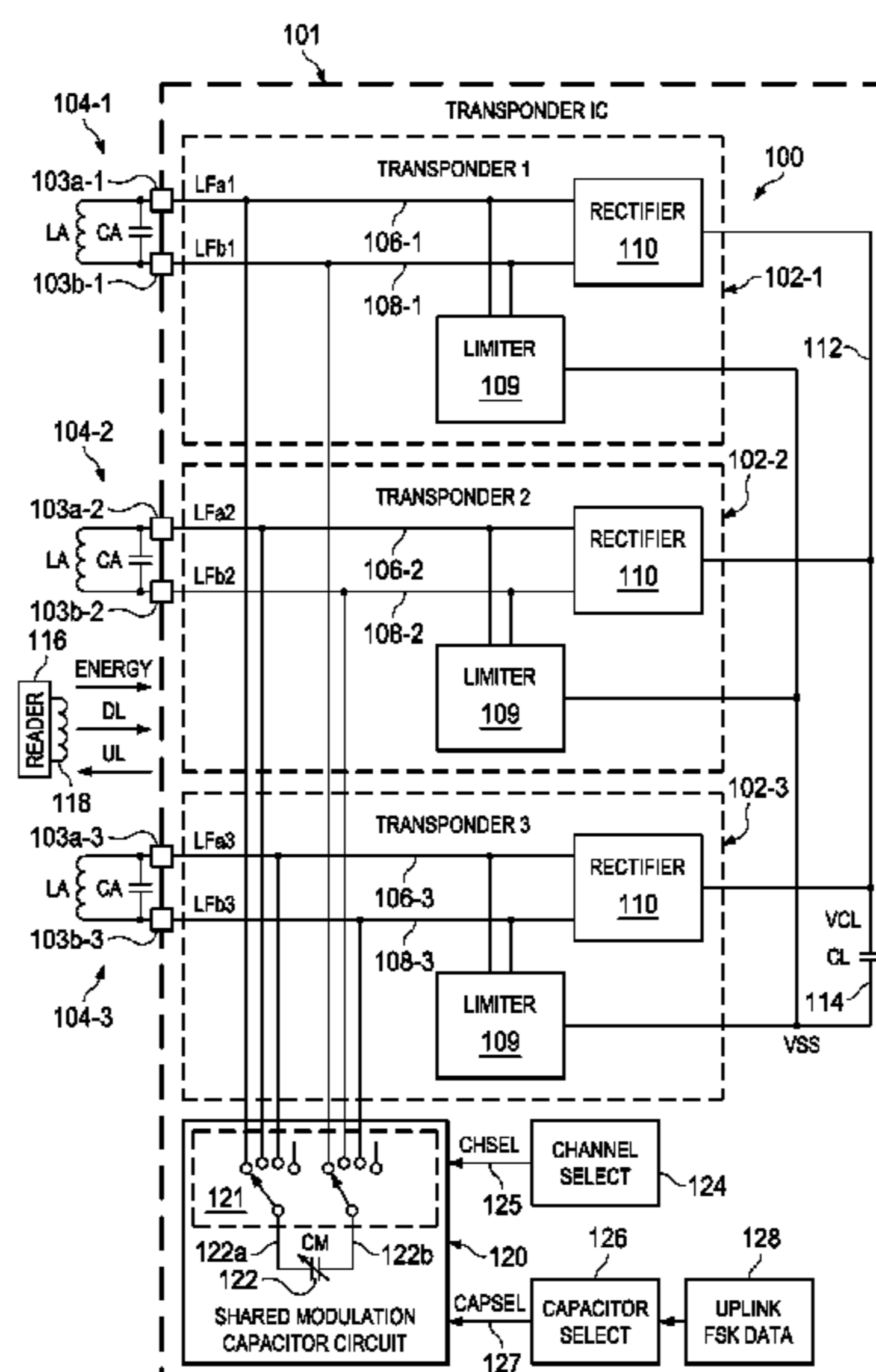
Disclosed examples include multichannel RF transponder circuits with multiple transponder channel circuits individually connected to a corresponding antenna circuit, a configurable shared modulation capacitor, a channel switching circuit to selectively connect the modulation capacitor to a selected transponder channel circuit, and a modulation circuit to selectively change the capacitance value of the modulation capacitor between two or more values according to a modulation control signal to transmit uplink data using the selected transponder channel circuit.

(51) **Int. Cl.**
H04L 27/12 (2006.01)
H04B 5/00 (2006.01)

(52) **U.S. Cl.**
CPC **H04L 27/12** (2013.01); **H04B 5/0068** (2013.01)

(58) **Field of Classification Search**
CPC H04L 27/12; H04B 5/0068
See application file for complete search history.

18 Claims, 11 Drawing Sheets



(56)

References Cited

U.S. PATENT DOCUMENTS

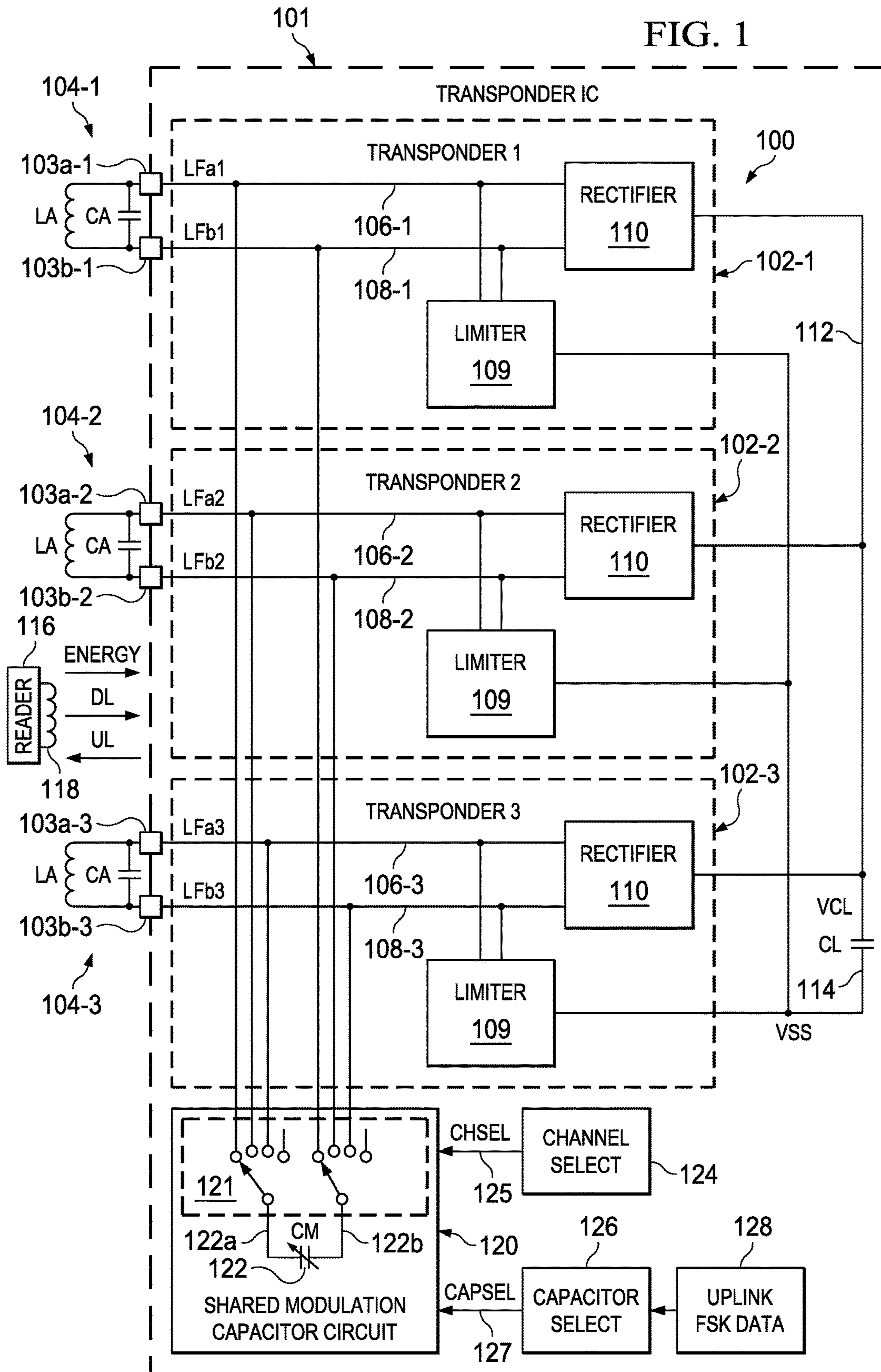
9,762,282	B1	9/2017	Muellner	
10,038,579	B1	7/2018	Muellner	
10,224,757	B2	3/2019	Muellner	
2002/0030617	A1	3/2002	Haroun et al.	
2002/0063622	A1*	5/2002	Armstrong	G06K 7/0008 340/10.31
2002/0158696	A1	10/2002	Staszewski	
2005/0237161	A1	10/2005	Lee et al.	
2005/0237163	A1*	10/2005	Lee	G06K 19/0723 340/10.51
2009/0174592	A1	7/2009	Muellner	
2009/0189688	A1	7/2009	Nehrig et al.	
2010/0141389	A1	6/2010	Hagl et al.	
2010/0253315	A1	10/2010	Nehrig	
2012/0092055	A1	5/2012	Peschke et al.	
2012/0153894	A1	6/2012	Widmer	
2012/0153903	A1	6/2012	Kim et al.	
2012/0161935	A1	6/2012	Ziegler	
2012/0161942	A1	6/2012	Muellner et al.	
2012/0194265	A1*	8/2012	Katsube	H03H 11/1252 327/554
2013/0009706	A1	1/2013	Peschke et al.	
2015/0145651	A1	5/2015	Muellner et al.	
2016/0328637	A1	11/2016	Viikari	

FOREIGN PATENT DOCUMENTS

RU		163740	U1	8/2016
WO		WO1999/030286	A1	6/1999

* cited by examiner

FIG. 1



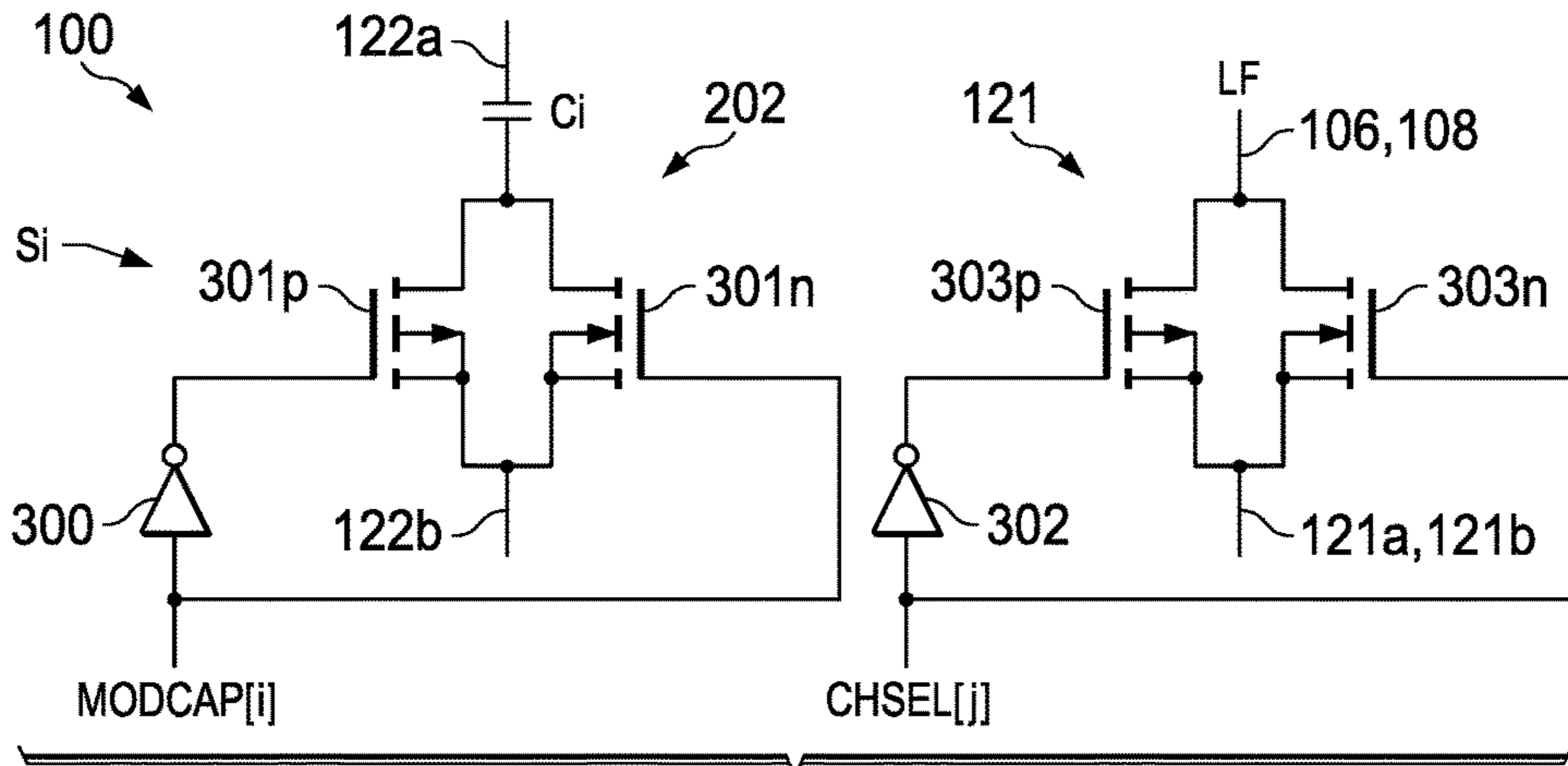


FIG. 3

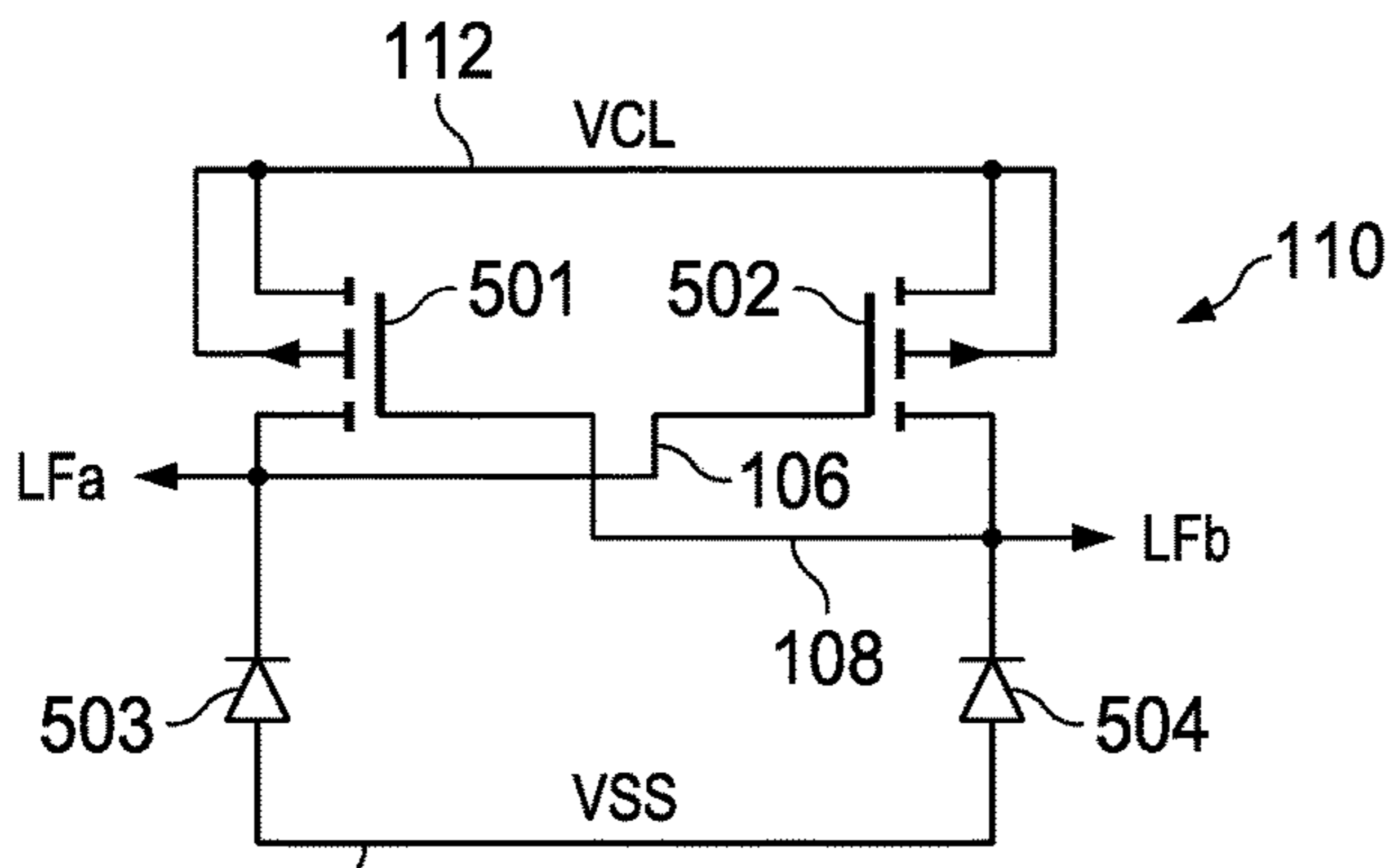


FIG. 6

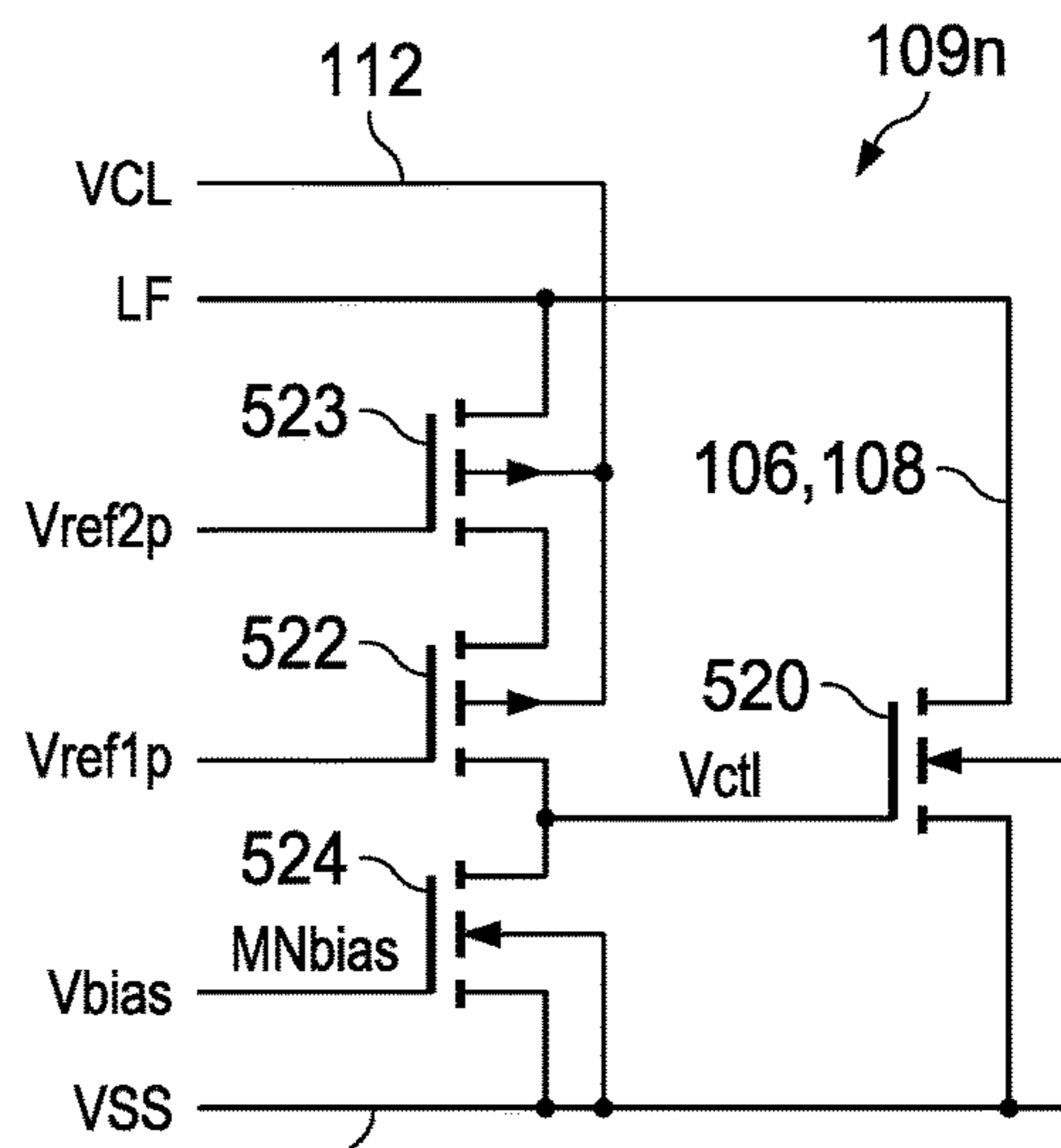


FIG. 7

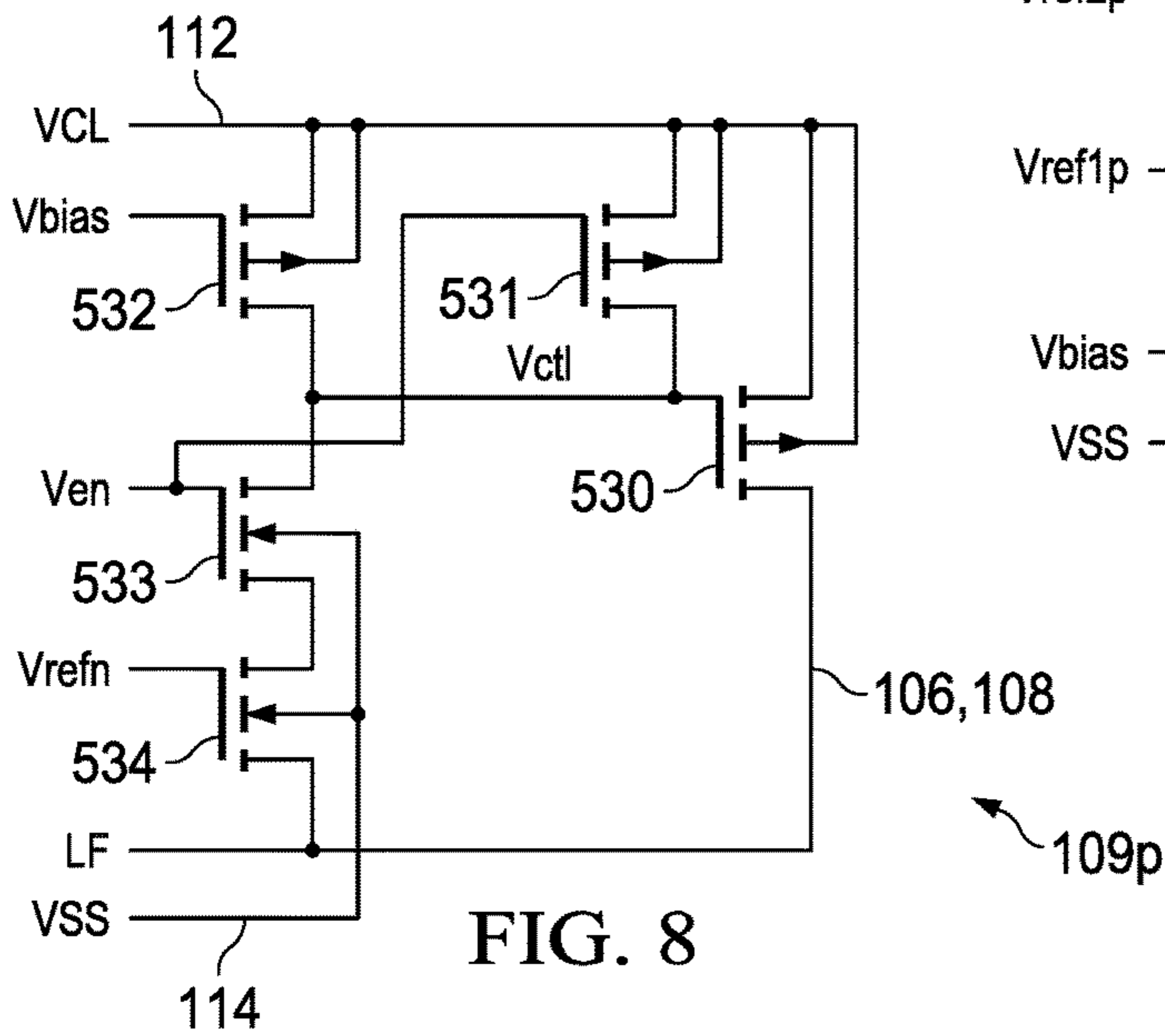


FIG. 8

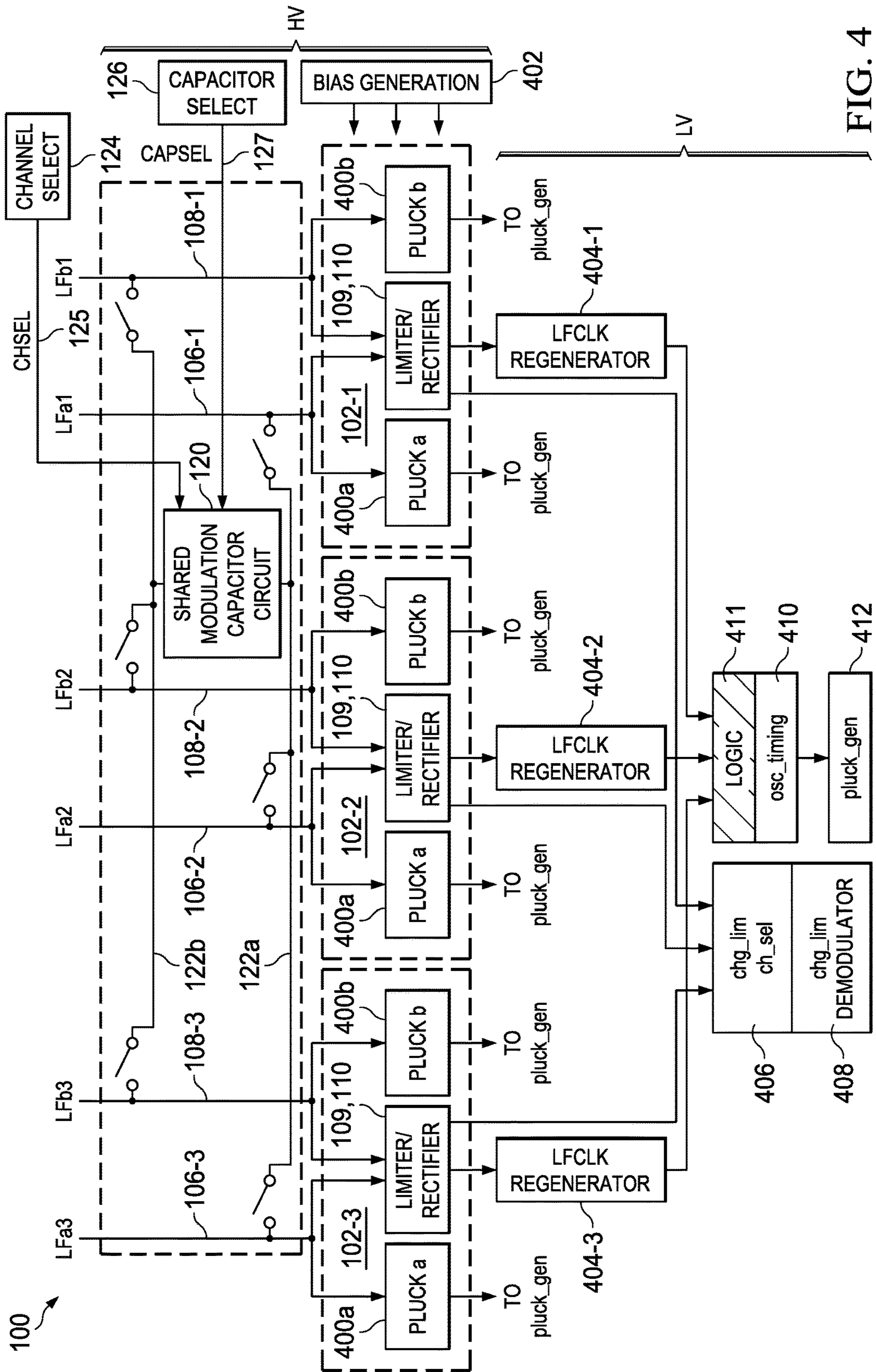
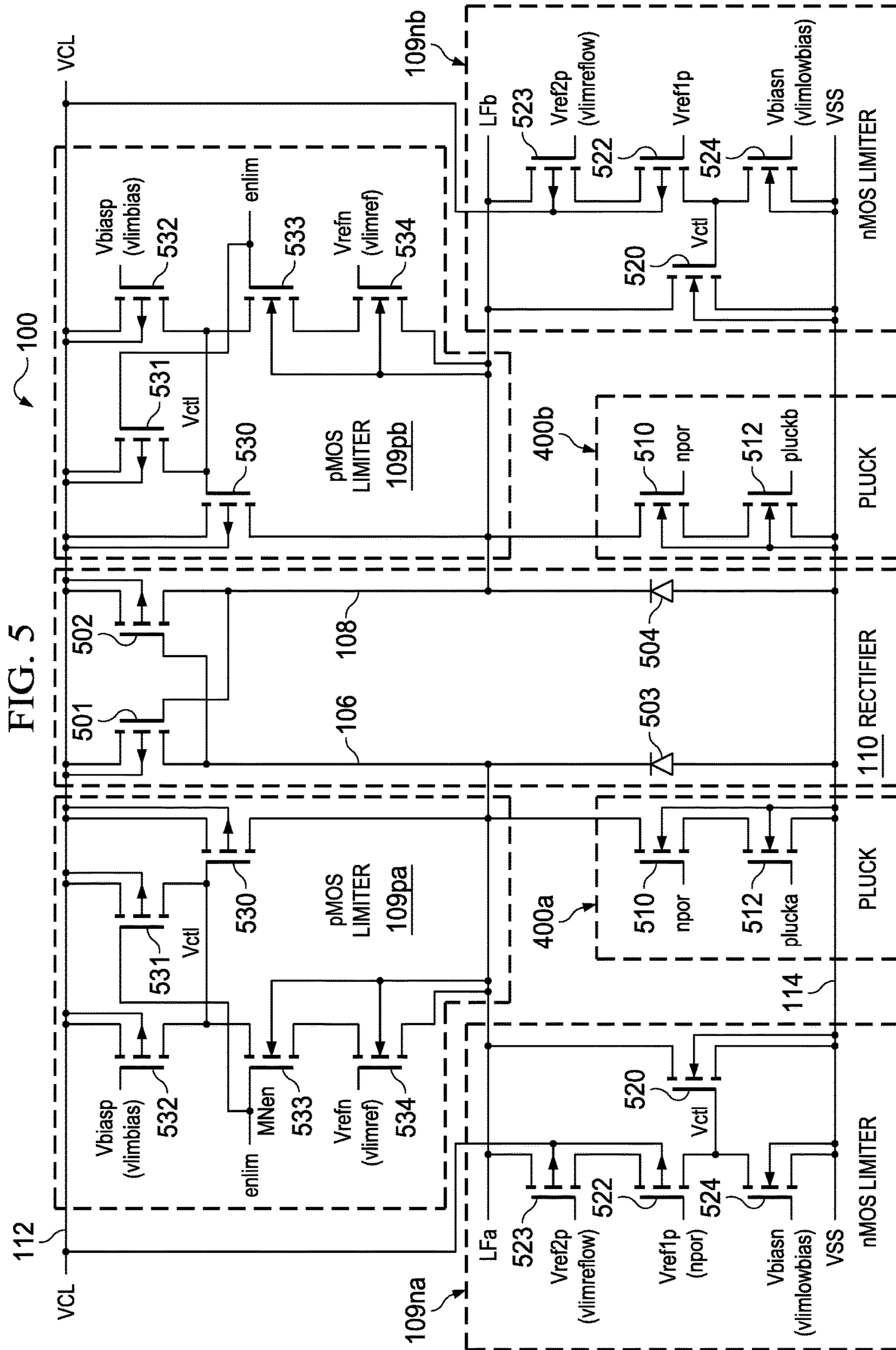


FIG. 4



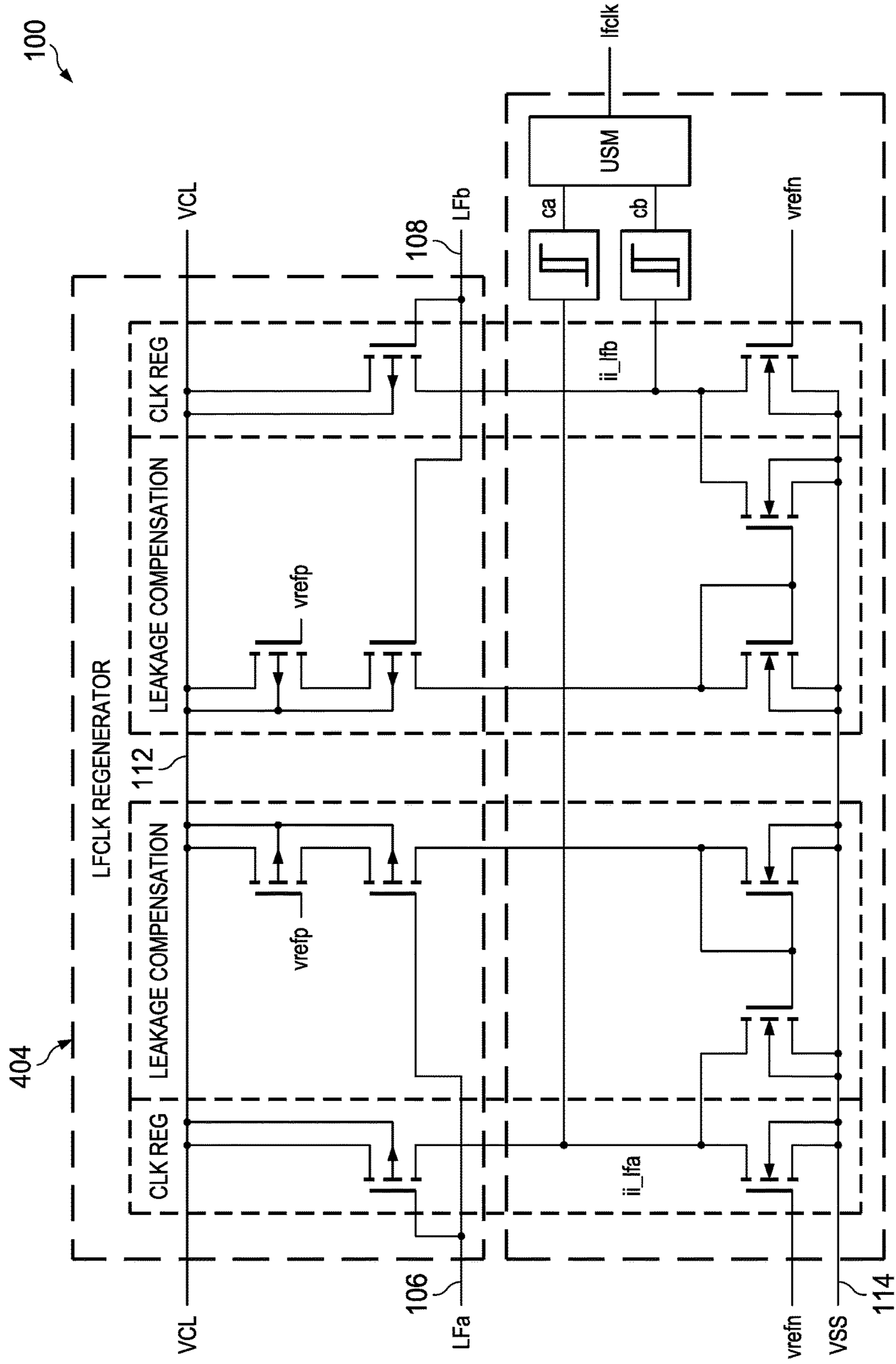


FIG. 9

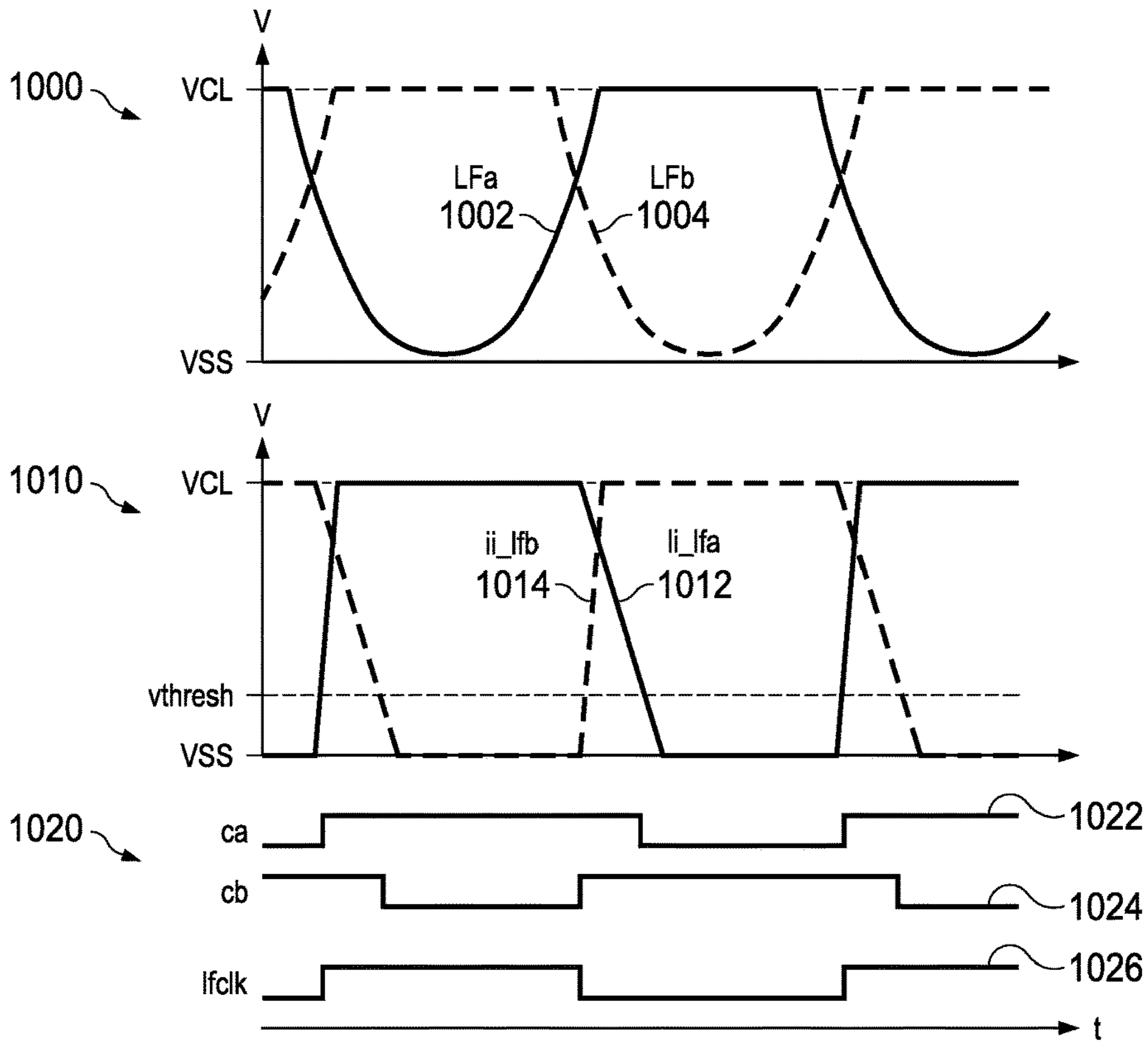


FIG. 10

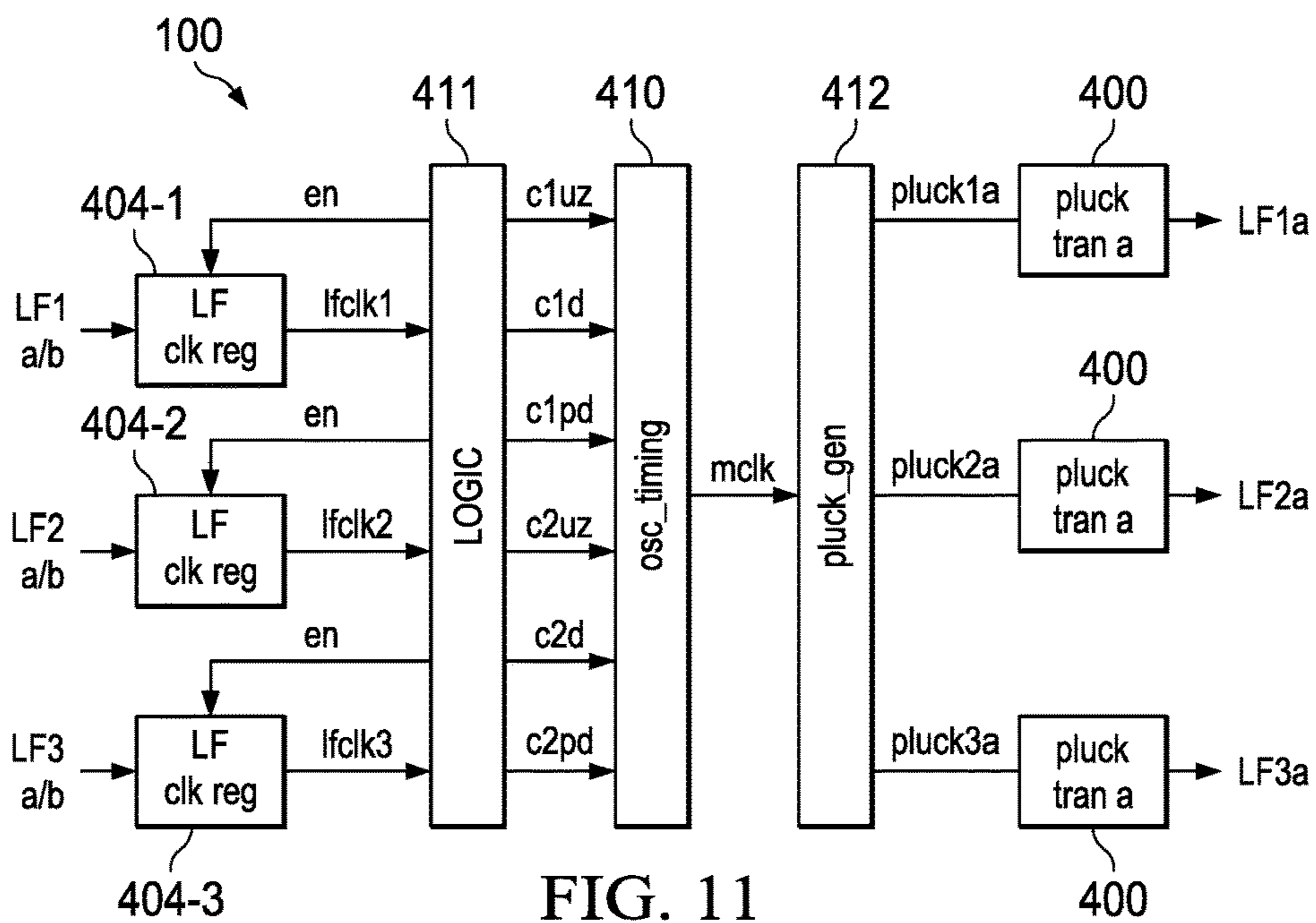


FIG. 11

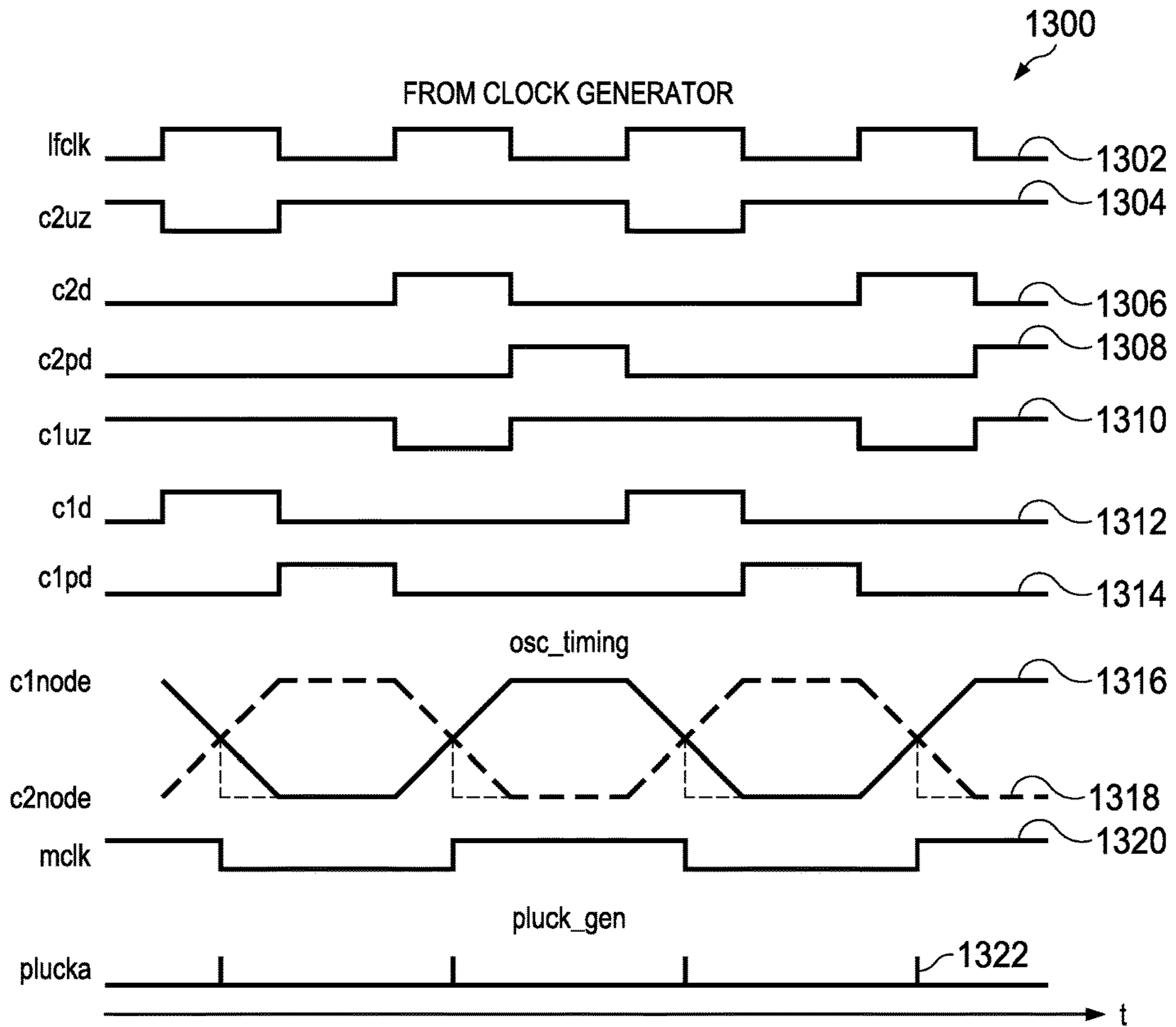
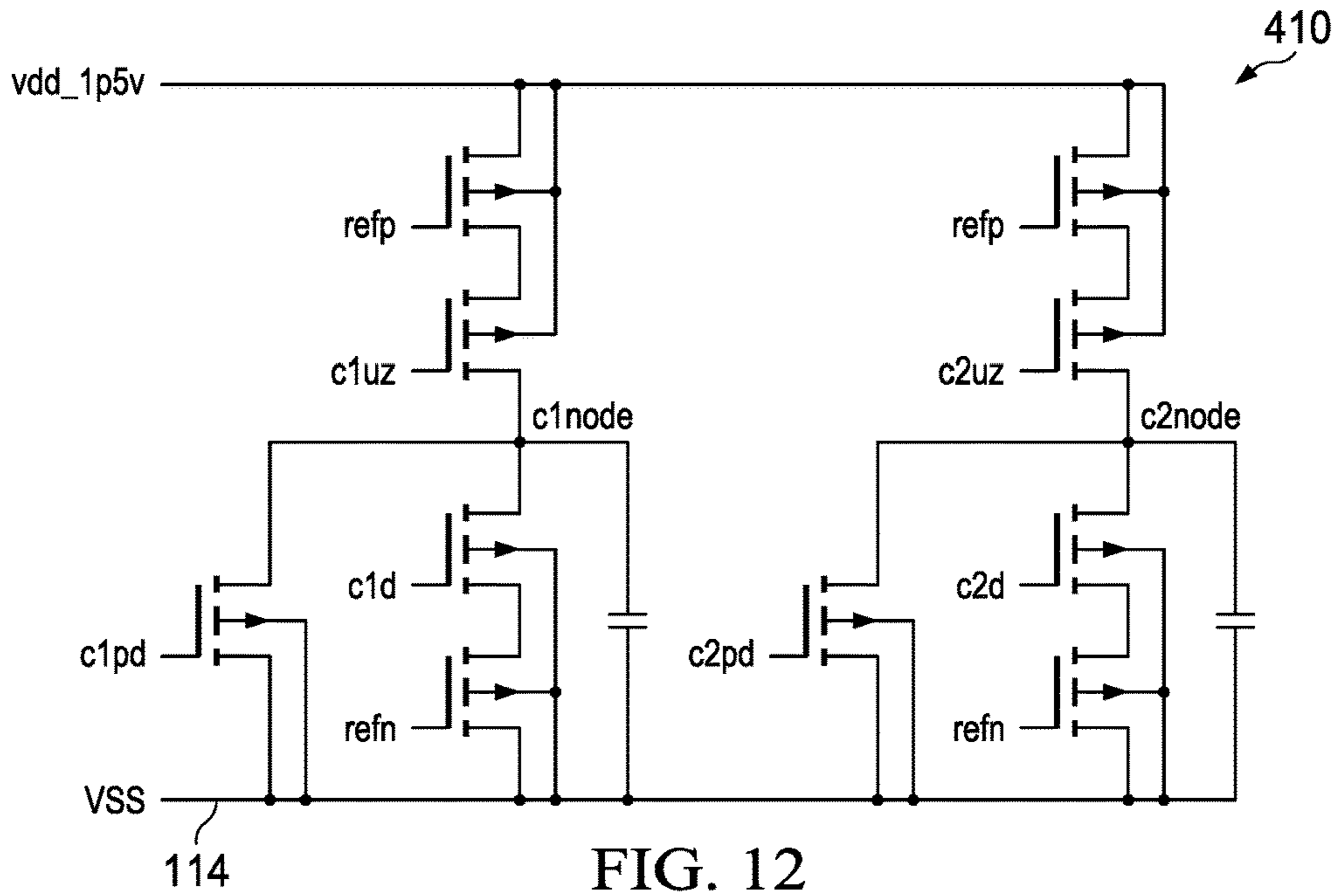


FIG. 13

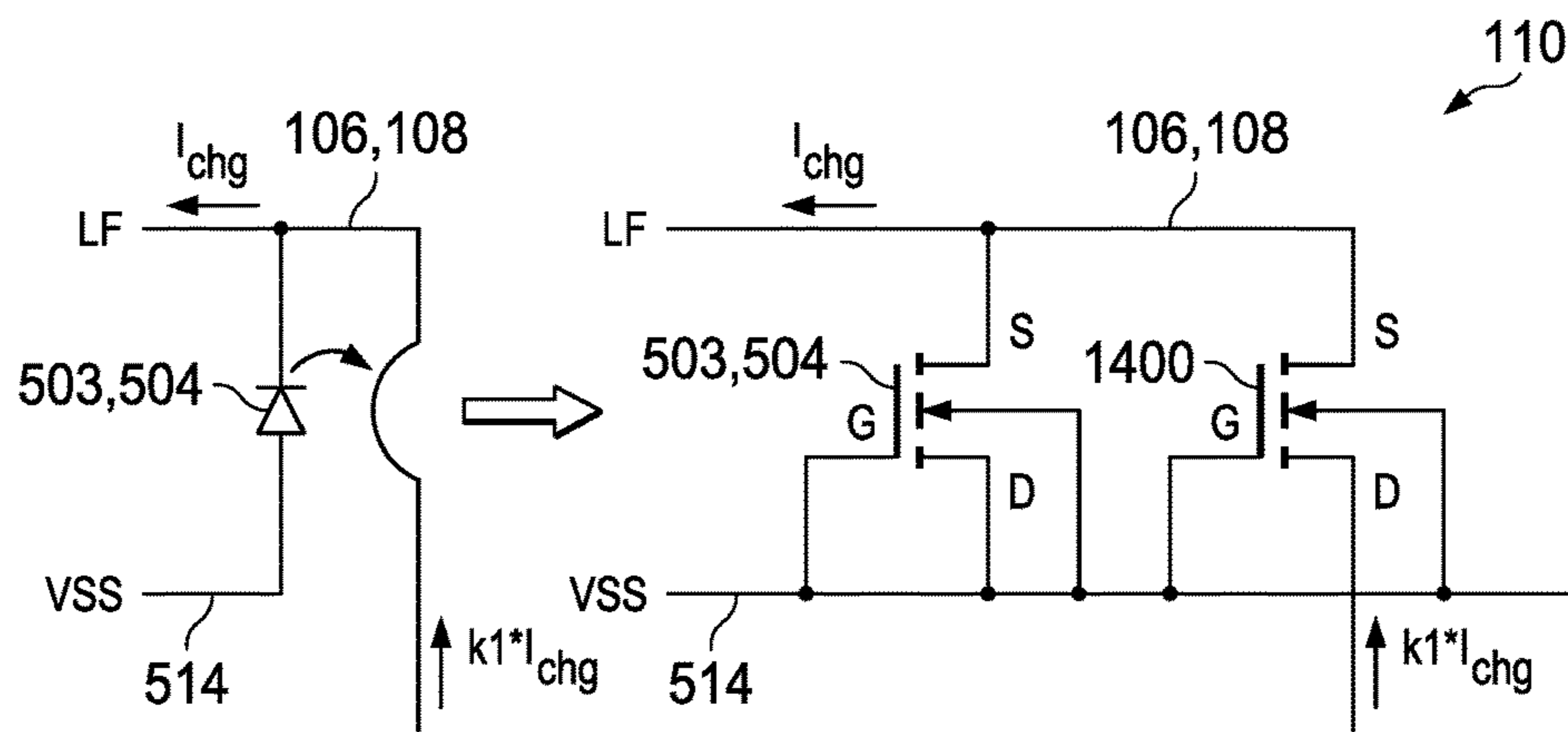


FIG. 14

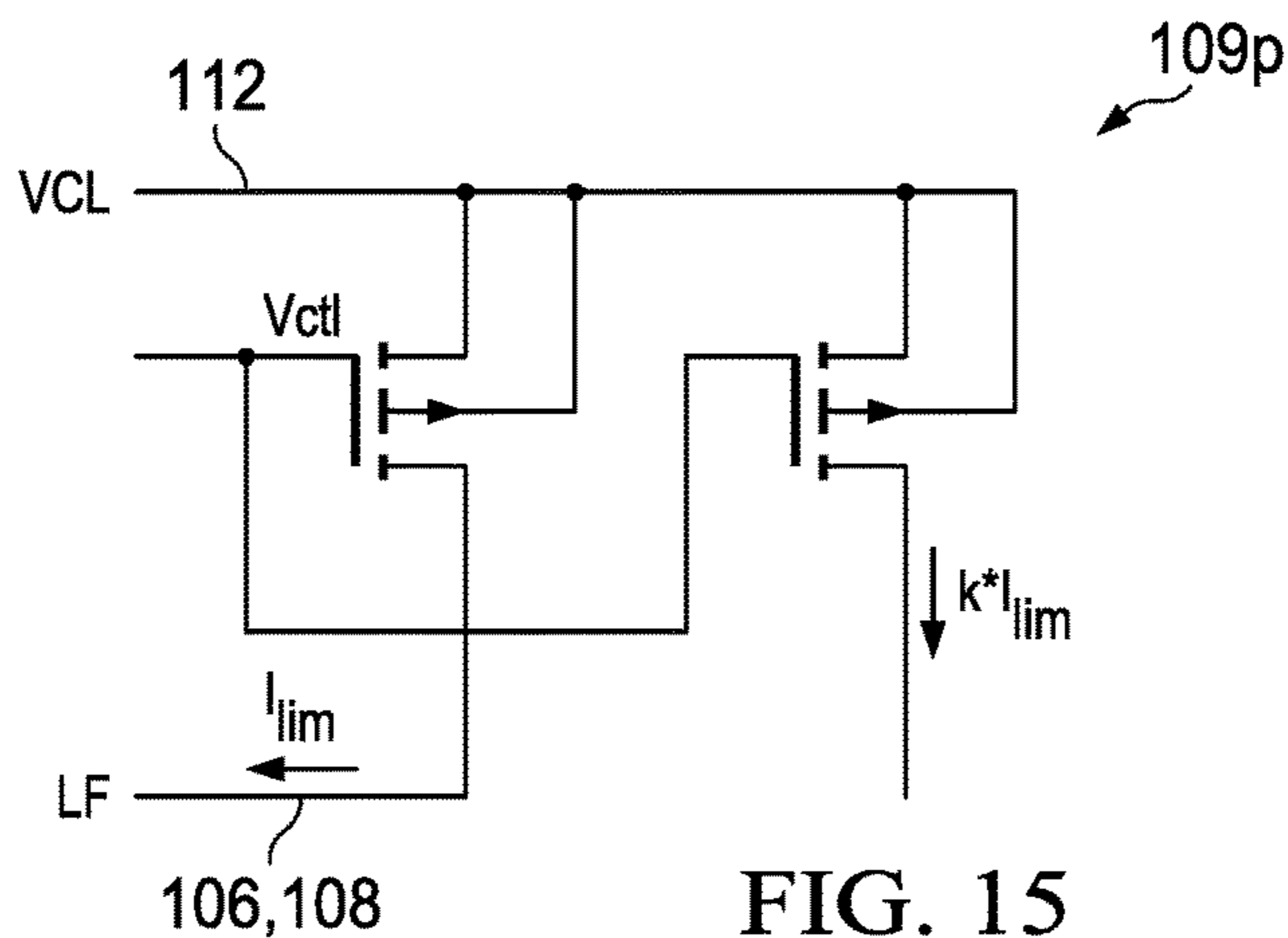


FIG. 15

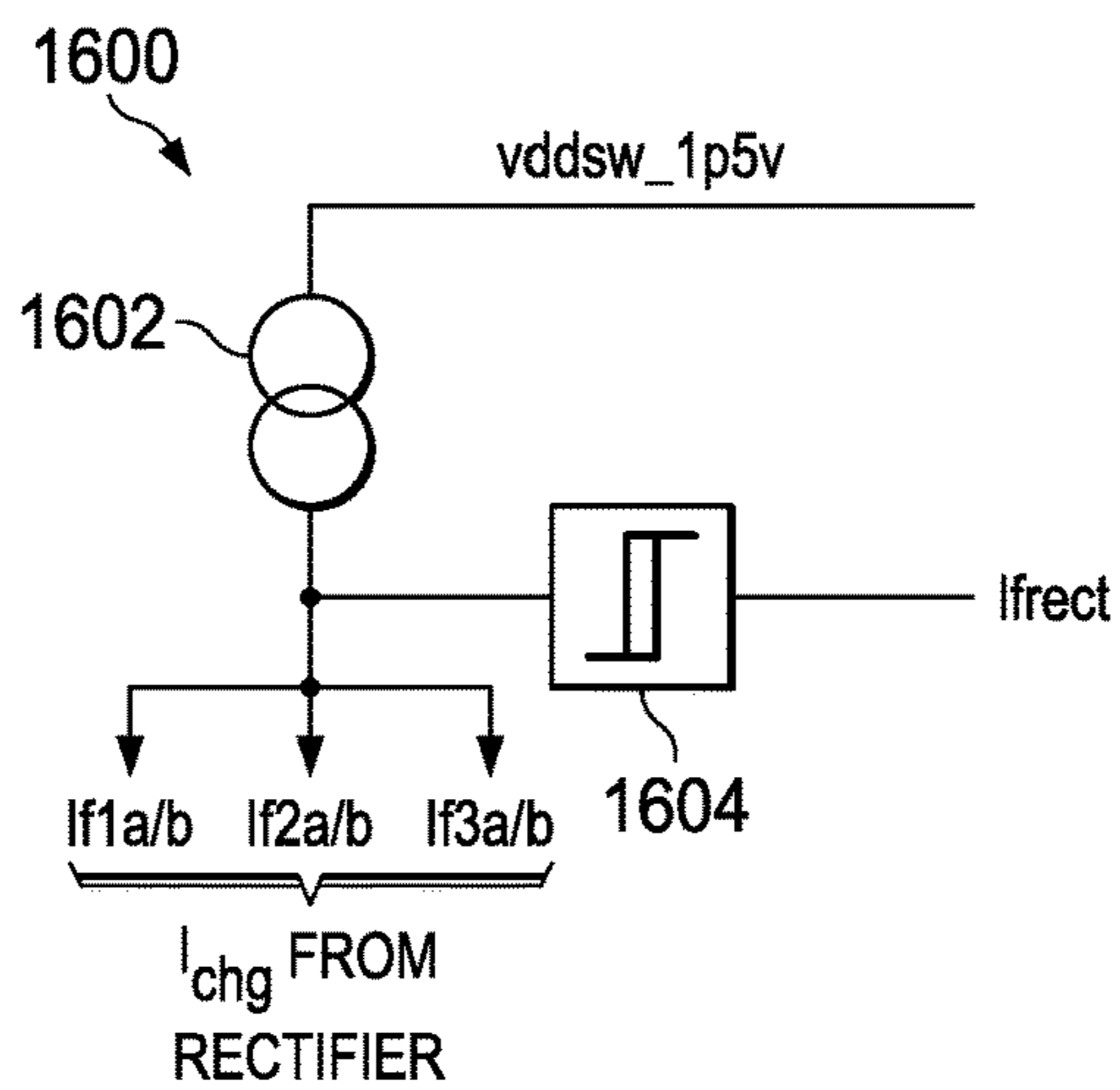


FIG. 16

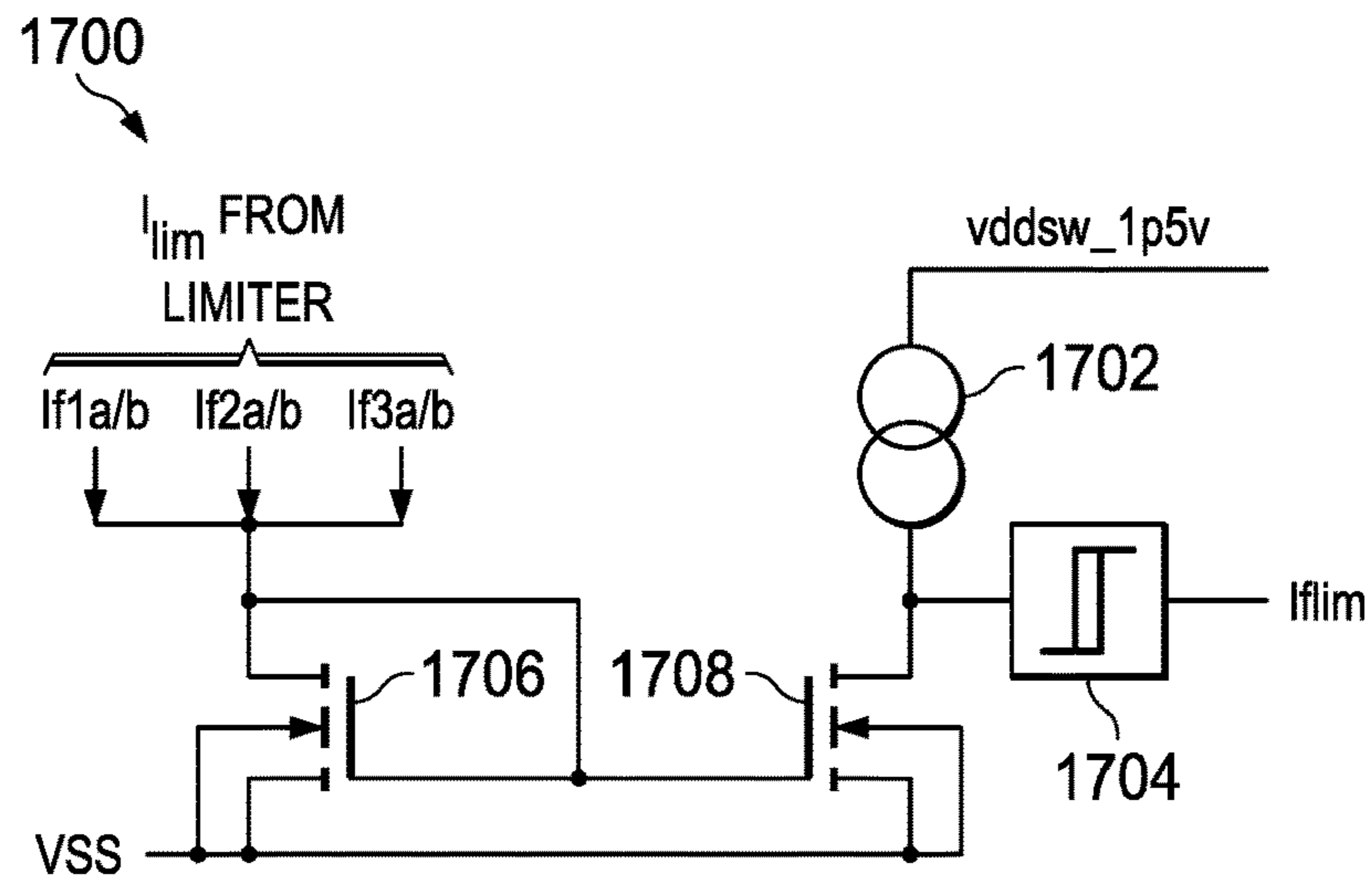


FIG. 17

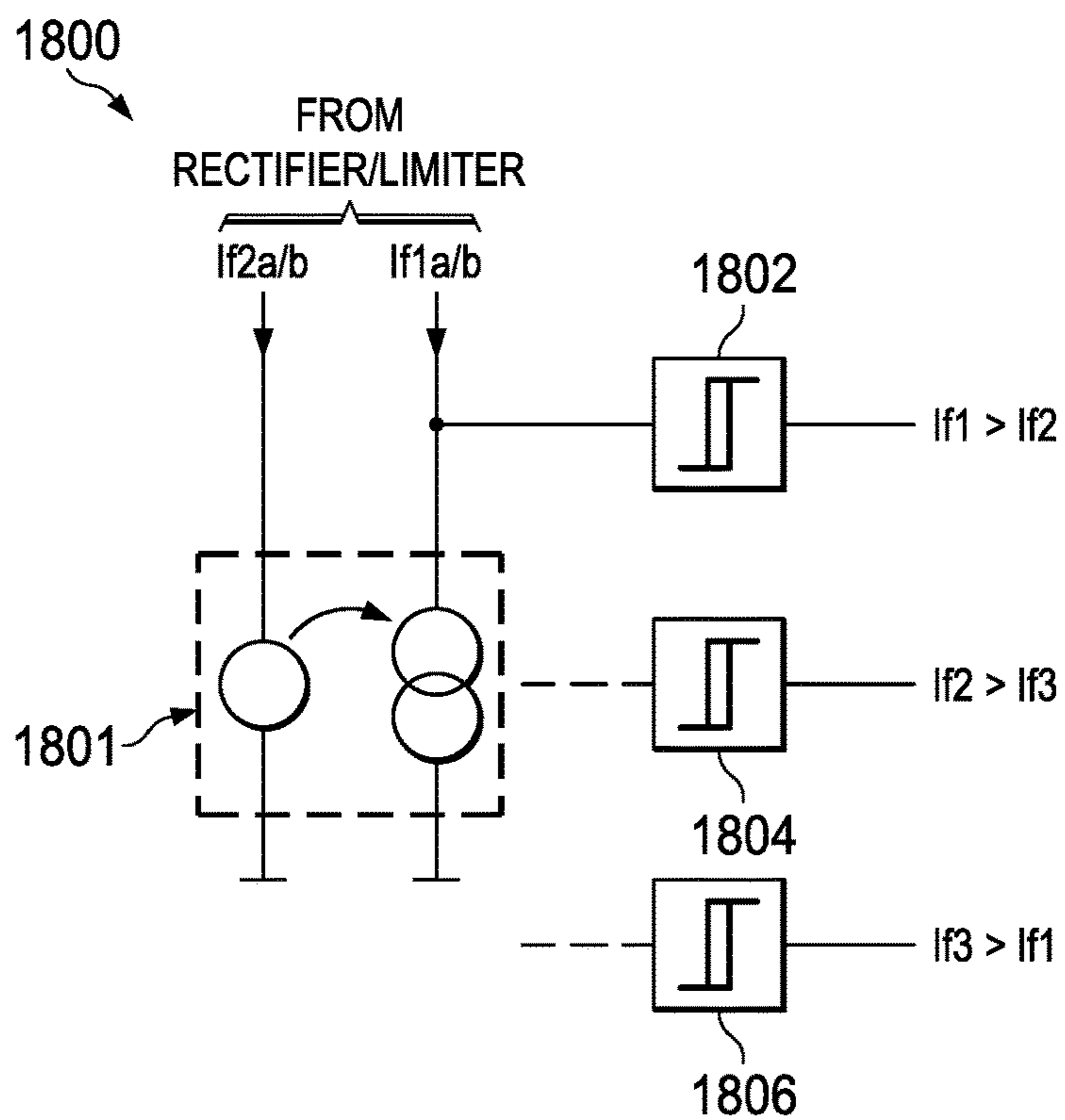


FIG. 18

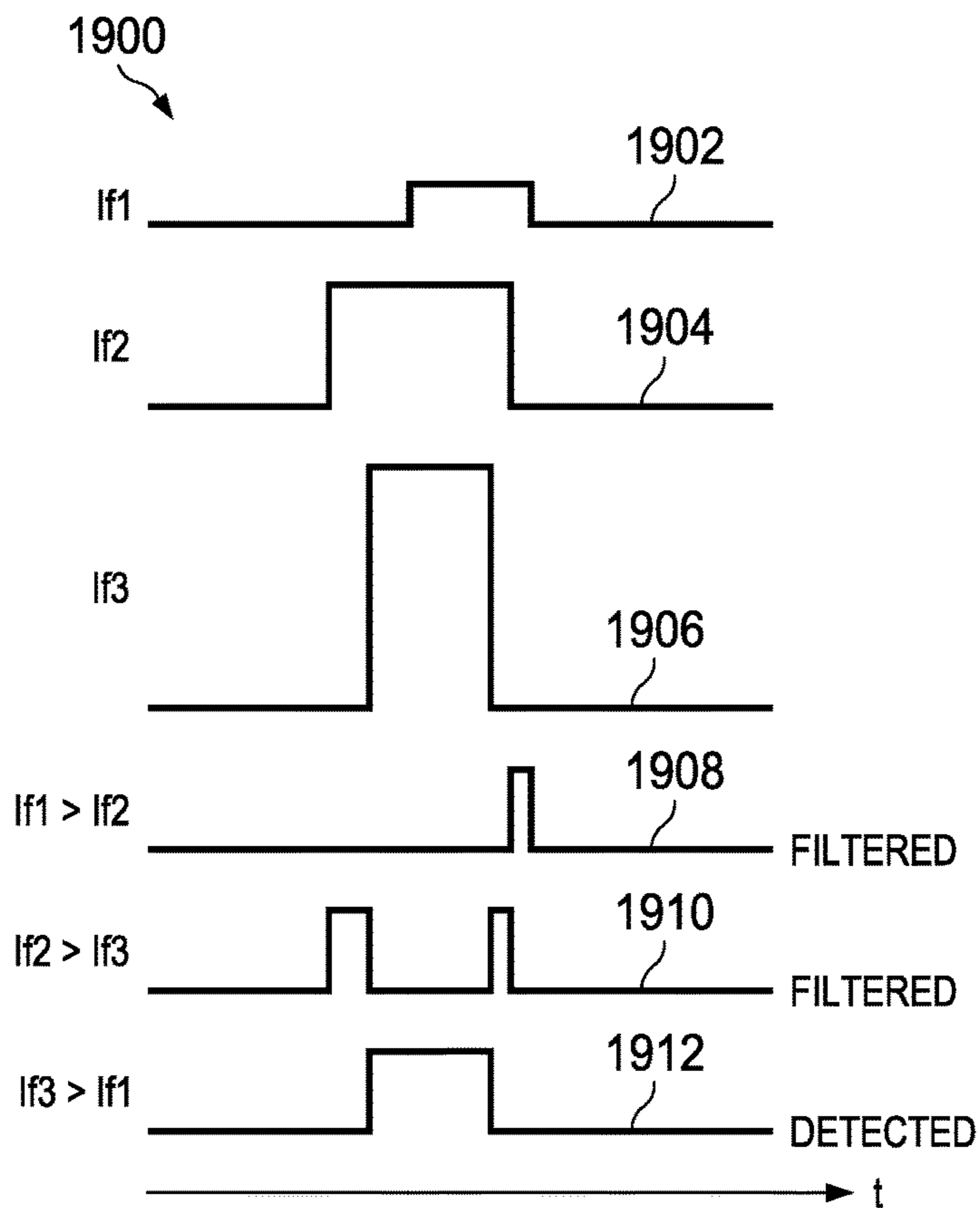


FIG. 19

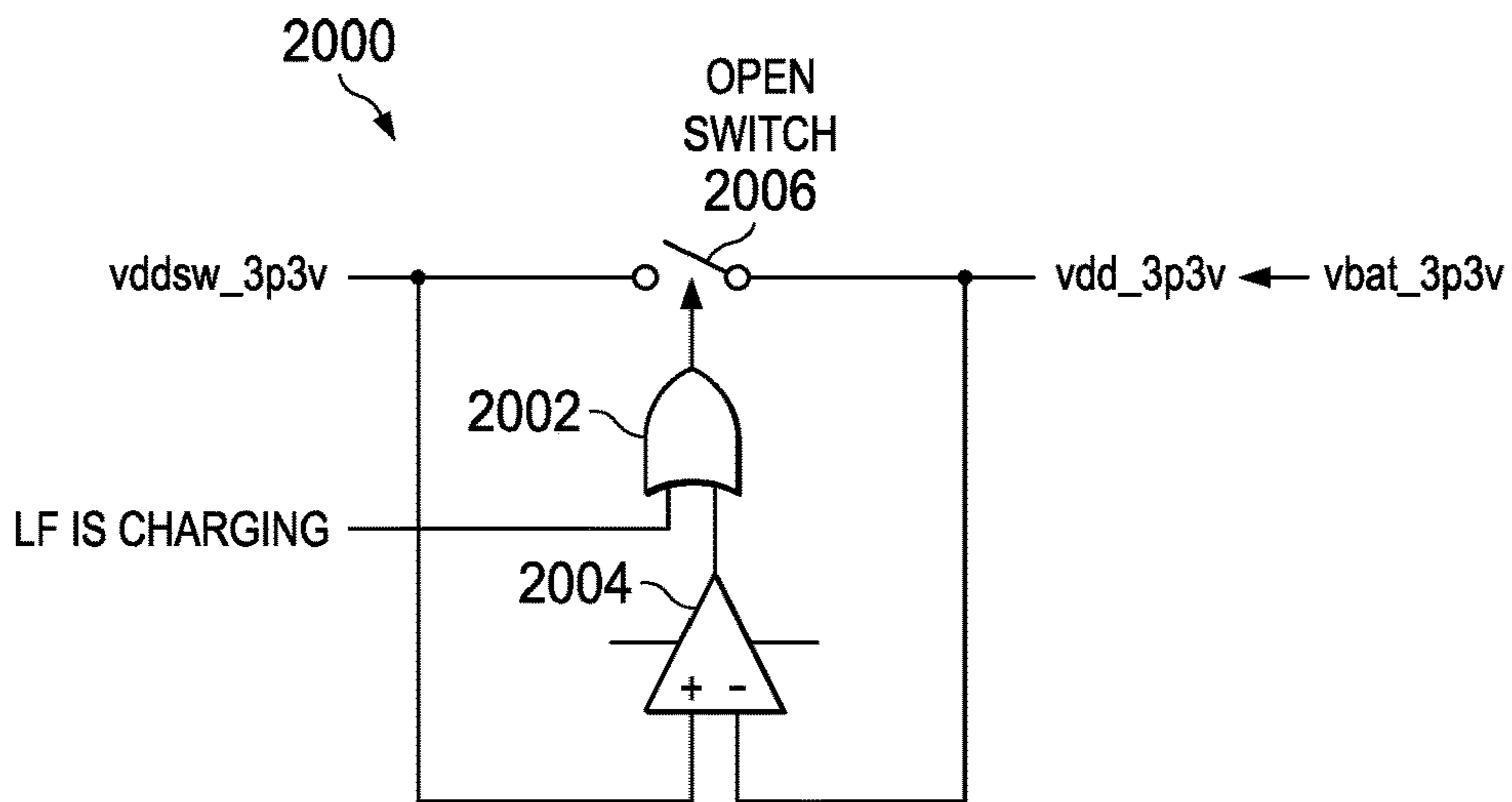


FIG. 20

1

**INTEGRATED CIRCUITS AND
TRANSPONDER CIRCUITRY WITH SHARED
MODULATION CAPACITOR FOR 3D
TRANSPONDER UPLINK MODULATION**

REFERENCE TO RELATED APPLICATIONS

This application is a continuation of U.S. patent application Ser. No. 15/459,696, filed on Mar. 15, 2017, and also relates to co-owned and co-assigned U.S. patent application Ser. No. 15/459,738, filed on Mar. 15, 2017 and entitled “INTEGRATED CIRCUITS AND TRANSPONDER CIRCUITRY WITH IMPROVED ASK DEMODULATION,” each of which is hereby incorporated by reference in their entirety.

BACKGROUND

The present disclosure relates generally to radio receivers and transmitters, and more particularly to multichannel radio frequency identification (RFID) transponders and systems. RFID transponders are typically small devices that may include a battery to power internal circuitry, but often operate using energy that can be harvested from an RF field generated by an RFID reader. Low-power transponders often begin operation with zero internal power and generate internal supply power using energy received through a transponder antenna. In operation, the transponder receives a specific RF signal from a reader, and responds by transmitting an RF signal with specific characteristics that can be detected by the reader. The RF signals generated by the reader and transponder are typically modulated with data, allowing data exchange between the reader and the transponder. This feature of low-power RF transponders is useful in a variety of applications, such as automotive devices. RF transponders include an antenna to receive signals and/or energy from a reader, as well as to transmit data to the reader. The data and power reception is typically dependent upon the relative orientation of the reader antenna and the transponder antenna.

Multichannel (e.g., 3-D) transponders are useful where the relative positioning of the reader and the transponder is variable. For example, automotive immobilizer systems include an RFID reader positioned in a fixed location in a vehicle, and a 3-D transponder is mounted to a key fob. A user may be allowed entry to a vehicle and/or permitted to press a start button to start the vehicle if the vehicle’s RFID reader properly detects the key fob transponder. However, the relative position of the fixed RFID reader antenna and the key fob-mounted transponder antennas is indeterminate. Accordingly, such immobilizer systems often use 3-D transponder antenna arrangements where a set of three antennas are mounted at mutually orthogonal orientations on the fob. The initial transmission of data from the reader to the transponder is referred to as downlink communications. Once a transponder receives data from the reader, the transponder replies with transmitted information referred to as uplink communications.

The uplink communication is often implemented using frequency shift keying or FSK communications, in which in which the data signal states are represented by two or more discrete frequencies of a carrier signal. The transponder often modulates a capacitor forming part of a resonant circuit that includes the transponder antenna in order to generate multiple RF signal frequencies for FSK uplink transmission. However, such multichannel transponders require multiple FSK modulation circuits, which occupy

2

space on a circuit board or integrated circuit die. Where more than two FSK data states are used for uplink communications, additional modulation capacitors are needed, which further exacerbates the problem.

SUMMARY

Disclosed examples include multichannel RF transponder systems and integrated circuits with multiple transponder channel circuits individually connected to a corresponding antenna circuit. Transponder system includes a configurable shared modulation capacitor, and a channel switching circuit to selectively connect the modulation capacitor to a selected transponder channel circuit. A modulation circuit selectively changes the capacitance value of the modulation capacitor between two or more values according to a modulation control signal to transmit uplink data using the selected transponder channel circuit. In certain examples, the individual transponder system includes a cross-coupled full bridge rectifier to generate a supply voltage from a received RF signal.

BRIEF DESCRIPTION OF THE DRAWINGS

FIG. 1 is a schematic diagram of a multichannel RFID system with a 3-D transponder.

FIG. 2 is a schematic diagram of an example shared modulation capacitor circuit in the transponder of FIG. 1.

FIG. 3 is a schematic diagram of example switching circuits for channel and capacitor selection in the transponder of FIG. 1.

FIG. 4 is a schematic diagram of an example immobilizer including a 3-D transponder of FIGS. 1 and 2.

FIG. 5 is a schematic diagram of example rectifier, limiter and pluck circuits in the transponder of FIGS. 1 and 2.

FIG. 6 is a schematic diagram of an example cross-coupled full bridge rectifier circuit in the transponder of FIGS. 1 and 2.

FIG. 7 is a schematic diagram of an example NMOS limiter circuit in the transponder of FIGS. 1 and 2.

FIG. 8 is a schematic diagram of an example PMOS limiter circuit in the transponder of FIGS. 1 and 2.

FIG. 9 is a schematic diagram of an example clock regenerator circuit in the transponder of FIGS. 1 and 2.

FIG. 10 is a signal diagram of clock regenerator waveforms.

FIG. 11 is a schematic diagram of an uplink oscillator circuit in the transponder of FIGS. 1 and 2.

FIG. 12 is a schematic diagram of an example dual slope oscillator timing circuit in the transponder of FIGS. 1 and 2.

FIG. 13 is a signal diagram of uplink oscillator waveforms.

FIG. 14 is a schematic diagram of an example dual rectifier diode current mirror circuit in the transponder of FIGS. 1 and 2.

FIG. 15 is a schematic diagram of an example PMOS limiter current mirror circuit in the transponder of FIGS. 1 and 2.

FIG. 16 is a schematic diagram of an example diode mirror current signal generator circuit in the transponder of FIGS. 1 and 2.

FIG. 17 is a schematic diagram of an example limiter mirror current signal generator circuit in the transponder of FIGS. 1 and 2.

FIG. 18 is a schematic diagram of an example field strength comparator circuit in the transponder of FIGS. 1 and 2.

FIG. 19 is a signal diagram of field strength comparator waveforms.

FIG. 20 is a schematic diagram of an example immobilizer power switch circuit in the transponder of FIGS. 1 and 2.

DETAILED DESCRIPTION

In the drawings, like reference numerals refer to like elements throughout, and the various features are not necessarily drawn to scale. In the following discussion and in the claims, the terms “including”, “includes”, “having”, “has”, “with”, or variants thereof are intended to be inclusive in a manner similar to the term “comprising”, and thus should be interpreted to mean “including, but not limited to” In addition, the terms “couple”, “coupled” or “couples” are intended to include indirect or direct electrical or mechanical connection or combinations thereof. For example, if a first device couples to or is coupled with a second device, that connection may be through a direct electrical connection, or through an indirect electrical connection via one or more intervening devices and connections.

Referring initially to FIGS. 1 and 2, FIG. 1 illustrates a multichannel RFID system with a transponder circuit 100 formed in a 3-D transponder integrated circuit (IC) 101. FIG. 2 illustrates details of an example shared modulation capacitor circuit in the transponder IC 101 of FIG. 1. The transponder circuit 101 includes multiple transponder channel circuits 102 that are individually connected to a corresponding antenna circuit 104 to receive a radio frequency (RF) signal LFa, LFb. In the illustrated example, the transponder IC 101 includes three transponder circuits 102-1 (TRANSPONDER 1 in the drawing), 102-2 (TRANSPONDER 2) and 102-3 (TRANSPONDER 3). In other examples, any integer number M transponder circuits 102 can be used, where M is greater than 1. In FIG. 1, the transponder channel circuits 102-1, 102-2 and 102-3 are individually associated with a corresponding transponder antenna circuit 104-1, 104-2 and 104-3, respectively. The individual transponder antenna circuits 104 include an antenna with an inductance LA, and an antenna circuit capacitor CA. In one example, the transponder system of FIG. 1 can be used in an automotive vehicle immobilizer system in which the individual antennas are positioned in a key fob or user key device at different orientations from one another. For example, three mutually orthogonal antennas can be used in order to facilitate RF communications between the transponder system and an antenna 118 of a reader 116. As schematically shown in FIG. 1, the reader 116 transmits downlink data DL to the transponder system, for reception by one or more of the transponder antenna circuits 104. In operation, the transponder system responds by transmitting uplink data UL from a selected one of the transponder antenna circuits 104 to the reader antenna 118.

The individual transponder channel circuits 102-1, 102-2 and 102-3 including a signal input node pair including a first signal input node 106 and a second signal input node 108. The individual signal input node pairs 106, 108 are coupled to receive an RF signal LFa, LFb from the associated transponder antenna circuit 104. In the illustrated example, the IC 101 includes three externally accessible terminal pairs 103, for example, conductive IC pins or pads. The terminal pairs 103 are individually connected to a corresponding signal input node pair 106, 108 to receive a corresponding RF signal LFa, LFb from the associated transponder antenna circuit 104. In this example, the first terminal pair includes

a terminal 103a-1 connected to deliver a signal LFa1 to a signal input node 106-1 of the first transponder channel circuit 102-1, as well as a terminal 103b-1 connected to deliver a signal LFb1 to a signal input node 108-1 of the first transponder channel circuit 102-1. Similarly, a second terminal pair includes a terminal 103a-2 connected to deliver a signal LFa2 to a signal input node 106-2, and a terminal 103b-2 connected to deliver a signal LFb2 to a signal input node 108-2 of the second transponder channel circuit 102-2. In addition, a third terminal pair associated with the third transponder circuit 102-3 includes a terminal 103a-3 connected to deliver a signal LFa3 to a signal input node 106-3, and a terminal 103b-3 connected to deliver a signal LFb3 to a signal input node 108-3.

As shown in FIG. 1, the individual transponder channel circuits 102 include a channel rectifier circuit 110 connected to the corresponding signal input nodes 106 and 108, as well as a channel limiter circuit 109 also connected to the signal input nodes 106 and 108. Further details of an example limiter circuits are illustrated and described below in connection with FIGS. 5, 7 and 8. The individual transponder channel rectifier circuits 110 in certain examples are cross-coupled full bridge rectifier circuits. Example channel rectifier circuits 110 are further illustrated and described below in connection with FIGS. 5 and 6. The transponder channel rectifier circuits 110 generate a supply voltage VCL at a supply node 112 relative to a voltage VSS of a reference node 114 from a received RF signal LFa, LFb. The transponder IC 101 further includes a load capacitor CL connected between the supply voltage node 112 and the reference node 114. As discussed further below, the use of a full bridge rectifier circuit or circuits 110 advantageously facilitates control of the antenna voltages between the supply voltage VCL and the reference node voltage VSS (e.g., ground). This, in turn, facilitates switched sharing of a single modulation capacitor 120 for uplink communications using FSK. In operation, various circuitry of the transponder IC 101 is powered by the supply voltage VCL, and the rectifier circuits 110 establish or maintain the supply voltage VCL using energy derived from received RF signals at one or more of the antenna circuits 104. In this manner, the illustrated reader 116 in FIG. 1 delivers energy (schematically shown as ENERGY in FIG. 1) to power the transponder IC 101. In certain examples, the IC 101 is exclusively powered by received energy from an associated reader circuit 116. In other examples, the IC 101 can be powered by an associated battery to at least partially establish the supply voltage VCL (not shown), and the rectifier circuits 110 can be used to supplement battery-powered, or to power the IC 101 when the battery is discharged.

The transponder IC 101 and the transponder circuit 100 thereof include a modulation circuit with a configurable shared modulation capacitor 122 with a capacitance value CM, and a channel switching circuit 121 to selectively connect the modulation capacitor 122 to a selected transponder channel circuit 102. In addition, the transponder circuit 100 includes a modulation circuit 120, 126 to selectively change a capacitance value CM of the modulation capacitor 122 according to a modulation control signal CAPSEL, for example to transmit uplink data 128 using the selected transponder channel circuit 102 using frequency shift keying (FSK) communications. In operation, once the transponder circuit 100 receives downlink data DL from the reader 116, the transponder circuit 100 replies with uplink data 128, and transmits the uplink data UL to the reader 116 using a selected one of the transponder circuits 102. For FSK uplink communication, the transponder circuit 100 selectively

changes the capacitance value CM of the shared modulation capacitor **122** to modify the RF signal frequency using the resonant antenna circuit including the modulation capacitance CM , the selected antenna circuit antenna inductance LA and the antenna circuit capacitor CA . As deviously discussed, replicating switched capacitors for FSK signal modulation in each of the transponder channel circuits **102** requires significant semiconductor die or chip area, particularly for a 3-D transponder with three antenna circuits **104**. In typical 3-D transponder applications (e.g., automotive immobilizer systems), only one antenna circuit **100** for transmits uplink data back to the reader **116**. In the illustrated examples, a single shared modulation capacitor circuit **120** provides selective connection to a single one of the transponder channel circuits 1024 FSK uplink modulated communications. Disclosed examples thus provide significant advantages with respect to conserving semiconductor die area by sharing the capacitor **122** between the three transponder channels.

Referring to FIGS. 1-3, the modulation capacitor **122** in FIG. 2 includes first and second capacitor nodes **122a** and **122b** including a first capacitor node **122a** and a second capacitor node **122b**. The channel switching circuit **121** selectively connects the modulation capacitor **122** to a selected signal input node pair **106, 108** and associated IC terminal pair **103** according to the channel select signal $CHSEL$. Any suitable switching circuitry **121** can be used. FIGS. 1 and 2 schematically illustrated a set of two single pole, triple throw switches (**121a** and **121b** in FIG. 2) with poles connected to the first and second capacitor nodes **122a** and **122b**, and selectable connections of the poles to a corresponding selected signal input node **106, 108**. As seen in FIGS. 1 and 2, a channel select circuit **124** provides a channel select signal $CHSEL$ to a control input **125** of the shared modulation capacitor circuit **120** to operate the channel switching circuit **121**. FIG. 3 shows one example in which the channel switching circuit **121** includes complementary pass gates individually connected between a corresponding one of the capacitor nodes **122a, 122b** of the modulation capacitor **122** and a corresponding one of the signal input nodes **106, 108**. Only a single complementary pass gate circuit is shown in FIG. 3, with an inverter **302** receiving a corresponding channel select input signal $CHSEL[j]$, where $j=1-3$. The output signal from the inverter **302** controls the gate voltage of the PMOS transistor **303p**, and the signal $CHSEL[j]$ directly controls the gate voltage of the NMOS transistor **303n**. In the illustrated example, the circuits **121a** and **121b** of FIG. 2 each include three complementary pass gates, each of which includes an NMOS transistor **303n** and a PMOS transistor **303p** as shown in FIG. 3. The channel select circuit **124** in FIGS. 1 and 2 can use any suitable logic to select the particular transponder channel circuit **102** for use in transmitting the uplink data. For example, the uplink transmit channel circuit **102** can be selected according to a maximum downlink communications signal amplitude received from the reader **116** at the corresponding transponder channel circuit **102**.

As best shown in FIG. 2, the shared modulation capacitor circuit **120** includes a capacitor array **200** and a modulation control circuit **202** connected to the modulation capacitor **122** to selectively modify a capacitance CM of the modulation capacitor **122** according to the modulation control signal $CAPSEL$. The capacitor select circuit **126** in FIGS. 1 and 2 provides the control signal $CAPSEL$ to select the modulation capacitance CM as a single control signal or multiple control signals and an input **127** to the shared modulation capacitor circuit **120**. The capacitor array **200**

example of FIG. 2 includes 8 capacitors $C0, C1, C2, C3, C4, C5, C6$ and $C7$, and the modulation control circuit **202** includes 8 corresponding switches $S0, S1, S2, S3, S4, S5, S6$ and $S7$. Other implementations are possible in which the capacitor array **200** includes any integer number N capacitors Ci , where N is greater than 1, and the modulation control circuit **202** includes N modulation control switches Si . In certain examples where N is greater than 3, the capacitor selects circuit **126** can provide the control signal $CAPSEL$ to selectively set the shared modulation capacitance CM to one of at least four values, thus allowing four-level FSK modulation for uplink data transmission. The individual capacitors Ci include a first capacitor terminal connected to the first capacitor node **122a** and a second capacitor terminal connected to the corresponding switch Si . The individual modulation control switches Si including a first switch terminal connected to the second capacitor terminal of the corresponding capacitor Ci , and a second terminal connected to the second capacitor node **122b** as shown in FIG. 2.

In operation, the individual modulation control switches Si electrically connect the second capacitor terminal of the corresponding capacitor Ci to the second capacitor node **122b** when a corresponding switch control signal $MODCAP[i]$ is in a first state. The switches Si disconnect the second capacitor terminal of the corresponding capacitor Ci from the second capacitor node **122b** when the corresponding switch control signal $MODCAP[i]$ is in a second state. In this manner, the capacitor select circuit **126** provides a N -bit control signal **127** ($CAPSEL$) including N modulation capacitor switch control signals $MODCAP[i]$, where $i=0$ through $N-1$ (e.g., $MODCAP[0], MODCAP[1], MODCAP[2], MODCAP[3], MODCAP[4], MODCAP[5], MODCAP[6]$ and $MODCAP[7]$). The N switch control signals $MODCAP[0,i]$ individually control the N modulation control switches Si to set the capacitance CM of the modulation capacitor **122** between the first and second capacitor nodes **122a** and **122b**.

As seen in FIG. 3, in one example, the individual modulation control switches Si are complementary pass gates, each with an NMOS transistor **301n** and a PMOS transistor **301p**. Only a single one of the control switches Si is shown in FIG. 3. The complementary pass gate switch Si includes an inverter **300** that receives the corresponding switch control signal $MODCAP[i]$ and provides an output to control the gate voltage of the PMOS transistor **301p**. The switch control signal $MODCAP[i]$ directly controls the gate voltage of the pass gate NMOS transistor **301n**. In this manner, the control signal $CAPSEL$ determines which, if any of the N capacitors Ci is connected between the first and second shared modulation capacitor nodes **122a** and **122b**. In certain examples, the N capacitors Ci have different capacitance values. In certain examples, moreover, the capacitance values of the N capacitors Ci are binary weighted, although not a strict requirement of all possible embodiments. In the example of FIG. 2, the eight capacitors $C0, C1, C2, C3, C4, C5, C6$ and $C7$ have corresponding binary weighted values based on a capacitance unit " C ", where $C0=C, C1=2C, C2=4C, C3=8C, C4=16C, C5=32C, C6=64C$ and $C7=128C$, although not a strict requirement of all possible embodiments. The selection of binary weighted capacitors $C0-C7$ advantageously facilitates range adjustment to accommodate different transmit antenna inductance values LA , and allows FSK modulation between two or more capacitance values CM according to the modulation control signal $CAPSEL$. The disclosed examples thus provide easily adaptable solutions, including multichannel tran-

spander integrated circuits **101** and transponder circuitry **100** to transmit uplink data **128** using the transponder antenna circuit **104** associated with the selected transponder channel circuit **102** using FSK communications. In addition, as noted above, the shared modulation capacitor circuit **120** advantageously economizes circuit die space to provide multichannel transponder circuits of any desired number of channels N , and any desired number of FSK transmission levels (e.g., 2FSK, 4FSK). Moreover, the disclosed modulation capacitor circuitry provides for differential capacitor connection to the selected transponder channel circuit **102**. As the full bridge rectifier circuits **110** and the limiter circuitry **109** maintain the antenna voltages generally between the reference node voltage VSS and the supply voltage VCL, compact MOFET switching devices can be used for modulation. In one example (2FSK), two distinct data values (e.g., 2fsk1 and 2fsk0) are used to control the capacitor select switches S_i . In another example for 4FSK transmission, the configured values (e.g., 4fsk11, 4fsk10, 4fsk01 and 4fsk00) are used for switching control.

FIG. 4 shows an example low frequency (LF) immobilizer system implementation including a 3-D transponder circuit **100** as described above in connection with FIGS. 1 and 2. The immobilizer structure in one example is a complex IO with self-protecting input circuits, which can be implemented in an I/O ring of an integrated circuit die. The immobilizer I/O configuration in one example is divided into a high voltage (HV) portion, a low voltage (LV) portion and a bias generation portion or circuit **402**. In one example, the bias generation circuit **402** includes high-voltage components. The shared modulation capacitor circuit **120** of the HV portion is connected to the signal input node pairs **106**, **108** by corresponding channel select switches as discussed above. The LV portion of the immobilizer implements demodulator functions, low frequency (LF) field strength comparators with associated filtering, LF clock regenerator circuits **404**, uplink oscillator circuitry **410** and **411** with mid clock generator circuitry, and a pluck pulse generator circuit **412**. As seen in FIG. 4, the signal input node pairs **106**, **108** are also connected to corresponding limiter and rectifier circuitry **109**, **110** as shown and described above in connection with FIG. 1. In addition, the individual transponder channel circuits **102** include first and second “pluck” circuits **400a** and **400b** as shown in FIG. 4. Each channel circuit **102-1**, **102-2** and **102-3** has a corresponding low-frequency clock (LFCLK) regenerator circuit **404-1**, **404-2** and **404-3**. The low-frequency clock regenerator circuits **404** provide input signals to an oscillator timing circuit **410** that includes a logic circuit **411**. The pluck circuits **400** and the oscillator timing circuit **410** provide signals to a pluck generator circuit **412**. In addition, the limiter circuits **109** provide signals to a charge limiter and channel select circuit **406**, and to a demodulator charge limiter circuit **408**.

Referring now to FIGS. 5-8, FIG. 5 shows further details of one possible implementation of the rectifier, limiter and pluck circuits **110**, **109** and **400** in the high voltage (HV) portion of the transponder circuit **100**. As shown in FIG. 5, the pluck circuits **400a** and **400b** each include NMOS transistors **510** and **512** connected in series between the corresponding signal input node **106**, **108** and the second supply (reference) node **114** (VSS). The transistors **510** and **512** are respectively operated according to control signals $npor$ and $plucka/pluckb$. FIGS. 5 and 6 illustrate an example cross-coupled full bridge rectifier circuit **110** that can be used in the individual transponder channel circuits **102**. As best seen in FIG. 6, the rectifier circuit **110** includes cross coupled upper PMOS transistors **501** and **502** connected

between the supply voltage node **112** (VCL) and the signal input nodes **106** and **108**. A full bridge rectification is achieved by the transistor **501** and **502** as well as diodes **503** and **504**, where the diode **503** is connected between the reference voltage node **114** (VSS) and the signal node **106**, and the diode **504** is connected between the reference node **114** and the signal node **108**. In one example, isolated NMOS transistors can be used in a diode-connected configuration to implement the diodes **503** and **504**. In operation at start up, the transponder supply voltage VCL begins at 0 V, and a low-frequency RF signal LFa, LFb caused by transmission from the reader **116** (FIG. 1) eventually exceeds a threshold voltage V_T at the gate terminal of one of the PMOS transistors **501**, **502**. When either transistor **501** or **502** turns on, charging occurs through the transistor to the supply voltage node **112** to charge the load capacitor CL (FIG. 1). As the RF signal LFa, LFb oscillates, the rectifier circuit transistors **501** and **502** alternately turn on and off to continue charging the load capacitor CL, which increases the supply voltage VCL.

FIGS. 7 and 8 illustrate details of NMOS and PMOS limiter circuits **109n** and **109p**. A NMOS limiter circuit **109n** and a PMOS limiter circuit **109p** are provided for each of the signal input nodes **106** and **108** as shown in FIG. 5 (NMOS limiter circuit **109na** and PMOS limiter circuit **109pa** connected to the signal input node **106**, and limiter circuits **109nb** and **109pb** connected to the signal input node **108**). Each of the NMOS limiter circuits **109n** (FIG. 7) includes an NMOS power transistor **520** that is controlled by a signal v_{ctl} and is connected between the corresponding signal input node **106**, **108** and the lower supply node **114** (VSS). The NMOS limiter circuits **109n** also include PMOS transistors **522** and **523** controlled by gate signals v_{ref1p} and v_{ref2p} , respectively, as well as an NMOS transistor **524** controlled by a gate signal v_{bias} . The immobilizer circuit in FIG. 5 acts as an electrostatic discharge (ESD) protection circuit and also operates as a low-frequency (LF) overvoltage input protection circuit, which is operative to protect the transponder circuit **100** during powered operation and also with zero supply (VCL=0). The voltage LF in FIGS. 7 and 8 is limited to a value V_{lim} that is the higher of voltages V_{ref1p} and V_{ref2p} plus one threshold voltage of a PMOS transistor. A control voltage node V_{ctl} in FIGS. 7 and 8 is initially discharged to have a defined voltage for the case of no supply. As best seen in FIG. 8, each PMOS limiter circuit **109p** includes a PMOS limiter power transistor **530** coupled between the first supply node **112** (VCL) and the corresponding signal input node **106**, **108**. The PMOS limiter circuits **109p** also individually include NMOS transistors **533** and **534** respectively controlled by signals V_{en} and v_{refn} , as well as a PMOS transistor **531** controlled by the V_{en} signal and a PMOS transistor **532** controlled by the bias signal v_{bias} . The complementary PMOS limiter circuit in FIG. 8 is enabled by the signal V_{en} to limit the signal voltage LF relative to the supply voltage VCL to the lower of signal levels V_{refn} minus the threshold voltage of the NMOS transistors. The reference and enable signals are generated by a separate circuit (not shown) in one example, to enable the PMOS limiter circuitry once the supply voltage $VCL > 3V$. The NMOS limiter circuit **109n** limits both the voltages LF and VCL, since the rectifier circuitry **110** ties VCL to LF. With no supply voltage (e.g., $VCL=0$), the NMOS limiter circuit **109n** limits the input voltage/VCL to V_{ref1p} plus one PMOS transistor voltage drop (V_{TP}), which is high enough for a bandgap circuit to start up and release the reset. In this mode, V_{ref2p} is 0 and the PMOS limiter circuit **109p** is disabled. After the reset is released, V_{ref2p} is

set to VCL to provide a limiter function for LF voltages above VCL plus VTP in case of common mode signals while the PMOS limiter circuit **109p** remains disabled. When the supply voltage VCL exceeds 3V (or other predefined level), the PMOS limiter circuit **109p** is enabled with a reference voltage of approximately one PMOS transistor voltage drop (VTP). In this manner, the amplitude of the LF voltage is limited to the supply voltage VCL. In one example, with a nominal supply voltage VCL of 3.0 V, the limiter circuitry **109** limits the maximum gate voltage of the transistors to approximately 3.6V.

A reference voltage generator (not shown) operates in three different modes. On power up with a band gap not yet working, the NMOS limiters **109n** operate with a reference signal vlimreflow. In a second mode with the band gap working, but $VCL < 3V$, the LF voltage (FIG. 7) is limited by the rectifying mechanism to VCL plus a diode voltage. When the band gap is operating for $VCL > 3V$, the PMOS limiter is activated in the third mode with reference signals enlim and vlimref. The signal vlimreflow is used for the NMOS limiters **109n**. This limits the LF voltage to vlimreflow plus a PMOS transistor voltage drop (VTP) relative to VSS. In the presence of the LF signal (e.g., during power up by LF) the supply voltage VCL is also limited. The limited supply voltage is higher than the startup voltage of the bandgap and less than a predetermined value (e.g., 3V. The signal vlimreflow in one example is provided by a passive resistor/divider diode structure to facilitate reliable startup. In one example, the signal enlim is created by comparing the (divided) supply voltage with the bandgap voltage using an active bandgap, and an additional passive pull-down is used for reliable startup. The signal vlimref is derived from the signal enlim and is approximately one NMOS transistor voltage drop (VTN) above VSS. This limits LF to approximately VSS, and no further charging of the load capacitor CL occurs.

Referring now to FIGS. 4, 9 and 10, FIG. 9 shows a clock regenerator circuit example **404** and FIG. 10 shows clock regenerator waveforms in the circuit of FIG. 9. A graph **1000** in FIG. 10 illustrates example RF signal voltage curves **1002** (LFa) and **1004** (LFb), and a graph **1010** illustrates curves **1012** (ii_lfa) and **1014** (ii_lfb) representing signal waveforms in the circuit **404** of FIG. 9. In addition, a graph **1020** in FIG. 10 illustrates a ca waveform **1022**, a cb waveform **1024** and a low-frequency clock signal waveform **1026** (lfclk) produced by the clock regenerator circuit **404**. The clock regenerator (clkreg in FIG. 9) consists of a pair of PMOS transistors with the gate connected to Lf working against an NMOS constant current source. The output signals ii_lfx feed a comparator (with comparator threshold vthresh, not shown in FIG. 9). The example circuit in FIG. 9 includes hysteresis comparator circuits that generate outputs ca and cb, respectively shown as curves **1022** and **1024** in FIG. 10. In one example, the signals ca and cb are raw LF clock signals that may include duty cycle distortion. A USM circuit removes the duty cycle distortion, and provides the output signal lfclk shown as curve **1026** in FIG. 10. The LF regenerator circuit **404** includes current source circuitry for clock regeneration for each of the LFa and LFb signals, as well as leakage compensation circuitry to provide a clock signal lfclk based on the RF signals LFa and LFb at the signal input nodes **106** and **108**. In one example, current in an NMOS constant current source is low to keep the quiescent current low. For high temperature and fast PMOS process corner, the leakage of the clkreg PMOS could be higher than this current, so that the ii_lfa/b would never go below a threshold voltage vthresh. In one example, the

leakage current is compensated. For the PMOS off state, the resulting leakage current is added to the NMOS current source to compensate for the leakage. For the PMOS on state, the current of the leakage compensation is limited by a vrefp biased PMOS constant current source. Leakage compensation is advantageous for implementations using low threshold voltage PMOS transistors, and may be omitted in other implementations. For clarity the bias generation, cascode transistors and power down circuits are not shown in FIG. 9.

Referring now to FIGS. 11-13, FIG. 11 shows an example uplink oscillator circuit in the transponder of FIGS. 1 and 2. The uplink oscillator circuit in FIG. 11 includes LF clock regenerator circuits **404-1**, **404-2** and **404-3** that receive the associated RF signals LFa, LFb and provide enable signals en and LF clock signals lfclk1, lfclk2 and lfclk3 to a logic circuit **411**. The logic circuit **411** provides two sets of capacitor control signals to an oscillator timing circuit **410**, including up or charging signals for capacitors **c1** and **c2** (**c1uz** and **c2uz**) as well as discharging and pre-discharging signals **c1d**, **c1pd**, **c2d** and **c2pd**. The logic circuit **410** provides a mid-clock signal mclk to the pluck generator circuit **412**. The pluck generator circuit **412**, in turn, receives three signals pluck1a, pluck2a and pluck3a from the corresponding pluck transistor circuits **400a**, as also shown in FIG. 4 above. FIG. 12 shows an example oscillator timing circuit **410**, and FIG. 13 provides a graph **1300** showing signal waveforms in the oscillator timing circuit **410**. The graph **1300** includes a curve **1302** showing the lfclk signal, curve **1304** showing the **c2uz** signal, a curve **1306** illustrating the **c2d** signal and a curve **1308** illustrating an example **c2pd** signal. In addition, FIG. 13 includes a curve **1310** showing the **c1uz** signal, curve **1312** showing the **c1d** signal and a curve **1314** showing the **c1pd** signal in the circuit **410**. The graph **1300** also includes oscillator timing curves **1316** (**c1node**), **1318** (**c2node**) and **1320** illustrating the mid-clock signal mclk, along with a pluck generator output signal curve **1322** (plucka). In operation, two capacitors are alternately charged up (e.g., cxu) and discharged (e.g., cxd) for the on-phase of the clock via the dual slope oscillator timing circuitry in order to generate the mid-clock signal mclk. The uplink oscillator (FIG. 11) uses the antenna resonant circuit to set the oscillation frequency via the received LFa and LFb RF signals. The immobilizer logic circuit **411** enables the clock regenerator of the selected antenna/transponder channel circuit **102** and creates the control signals for the oscillator timing circuit **410**. These signals from the logic circuit **411** are synchronous to the LF clock. The oscillator timing circuit **410** uses a dual slope approach to identify the middle time of the clock phase as shown in FIGS. 12 and 13. In operation, this circuitry identifies the middle of the on phase (mclk) as the crossing of the capacitor voltage is for the same charge and discharge currents. Upon detection of this crossing, the circuitry discharges the capacitor with the falling edge to suppress chatter in one example. In addition, this capacitor is kept discharged via pre-discharge signals **cxd**.

The edge detection with a digital delay and an exclusive OR (XOR) of the signal mclock creates pulses, which control the pluck structure. The length of the pluck pulse is not critical, and a longer pulse can be selected by DFT features in the pluck generator circuit. This pulse replaces energy loss in the antenna resonant circuit and sustains the oscillation. An offset of the comparator and differences between capacitors are averaged out within two oscillations. An offset between charge and discharge currents leads to a deviation from the ideal mid, which is used to compensate

for the delay of the clock regenerator. The pluck circuitry in one example includes two transistors in series, one of which is connected to npor to avoid unintended plucking during power up. For the oscillator, only one pluck structure at LFxa is required, but the identical structure is placed at LFxb in certain examples.

Referring now to FIGS. 4 and 14-17, the demodulator circuit in one example uses a current mirror technique to ascertain current flow in the rectifier and limiter circuit components (e.g., 501-504) which carry the charge or the limit current in FIG. 4. As discussed above, this circuitry is replicated for each of the individual transponder channel circuits 102 (FIG. 1), and provides signals that can be used by the transponder IC 1012 intelligently select the particular transponder channel for use in uplink communications based on various factors, such as received signal strength of downlink communications from the reader 116. FIG. 14 illustrates a dual rectifier diode current mirror circuit 1400, which can be used to measure the current flowing in the diode 503 or 504 of the rectifier circuit 110. In this case, charging current I_{chg} flows from the corresponding individual signal input node 106 or 108 to charge the load capacitor CL (FIG. 1) to establish the supply voltage VCL. On the left side of FIG. 1, a current mirror circuit is schematically shown to conduct a mirrored current $k \cdot I_{chg}$ that is proportional to the charging current use to charge the load capacitor CL (I_{chg}). The right side of FIG. 14 illustrates a circuit example using a diode-connected NMOS transistor 503, 504 to implement the lower rectifier diode, as well as a corresponding NMOS current mirror transistor to provide the mirrored current signal $k \cdot I_{chg}$. In operation, circuitry of the transponder IC 101 can use the mirrored current signal $k \cdot I_{chg}$ in operation of the transponder circuits 102 and/or the communications circuitry of the IC 101 based on the charging condition or state of the rectifier circuit 110 and/or of the supply voltage VCL and the load capacitor CL.

FIG. 15 shows an example of current mirroring to derive a limiting current signal $L \cdot I_{lim}$ corresponding to a limiter current I_{lim} in the PMOS limiter circuits 109p (also shown in FIG. 4 above). FIG. 16 illustrates an example diode mirror current signal generator circuit 1600 with a current source 1602 and a hysteresis circuit 1604 in the transponder of FIGS. 1 and 2. The current source 1602 operates from a reference voltage signal vddsw_1p5v to provide a current signal divided into the charge current signals (I_{chg}) from the LFa and LFb sides of the three rectifier circuits 110. The comparator circuit 1604 compares the voltage of the lower terminal of the current source 1602 with a reference, and generates a rectifier current level signal Ifrect. FIG. 17 is a schematic diagram of an example limiter mirror current signal generator circuit 1700 in the transponder of FIGS. 1 and 2. The circuit 1700 includes a reference current source 1702 that operates from the supply voltage signal vddsw_1p5v. The limiter current mirror signals I_{lim} from the circuit of FIG. 15 for each of the three transponder channels are summed at a summing node and provided to a current mirror transistor 1706. The summed limiter current is mirrored to a second transistor 1708 connected in series with the reference current source 1702. The circuit 1700 also includes a hysteresis comparator circuit 1704 that compares the lower terminal of the reference current source 1702 with a threshold and provides a limiter current level signal Iflim. As also shown in FIGS. 5 and 6, the circuit components 501-504 that form the cross-coupled full bridge rectifier circuit 110 carry the charge current or the limit current operation of the transponder circuit 100. As seen in FIGS. 15-17, elements of the same type but with less width and

with the same/similar operating condition are used as current mirrors to deliver current signals, which are a fraction of the charge and limit currents. In certain examples, these current mirror signals indicate the operating condition of the transponder. In one example, the sensed current mirror signals are pulse traces, which occur with a frequency of twice the carrier frequency. LFon is asserted if charge or limit condition is detected. In one example, the LFon signal is generated as lfchg or lflim, and is filtered in the digital domain.

FIGS. 18 and 19 illustrate example field strength comparison features of certain transponder IC embodiments. FIG. 18 shows an example field strength comparator circuit 1800 in the transponder of FIGS. 1 and 2. FIG. 19 is a signal diagram 1900 that shows an example field strength comparator signal sequence before filtering in the circuit 1800 of FIG. 18. FIG. 19 shows example signal curves 1902 (lf1), 1904 (lf2) and 1906 (lf3) representing sensed currents in the respective first, second and third transponder channel circuits 102-1, 102-2 and 102-3 of FIG. 1. A current mirror circuit 1801 in FIG. 18 mirrors a current sense signal from the second transponder circuit 102-2. A summing junction sums the mirrored current signal with a current sense signal from the first transponder circuit 102-1. A first hysteresis comparator circuit 1802 compares the resulting summing junction voltage with a threshold and generates a first comparator signal having a first state (e.g., low or logic "0") when lf1 is less than or equal to lf2, and a different second state (e.g., high or logic "1") when lf1 is greater than or equal to lf2. The output signal of the comparator 1802 is filtered using a low pass filter circuit (not shown) in one example. The filtered comparator output signal is shown as curve 1908 in FIG. 19 (lf1>lf2). The circuit 1800 includes further mirror circuits (not shown) and corresponding hysteresis comparators 1804 and 1806 and (and optionally associated output filters, not shown) to generate signals for the other two comparisons lf2>lf3 (curve 1910 in FIG. 19) and lf3>lf1 (curve 1912). In one example, the field strength comparators of the circuit 1800 use the same mirrored sense currents that are used for the demodulator, where the mirrored sensed currents are proportional to the field strength, the current pulses have similar widths, and the current pulses occur with only a minor shift. In the example of FIG. 19, the curves 1902, 1904 and 1906 show the current pulses with different heights (for one half the LFa or LFb RF signal period), and the curves 1908, 1910 and 1912 illustrate the resulting comparator outputs.

FIG. 20 shows an example immobilizer power switch circuit 2000 with an AND gate 202, a comparator 2004 and a power switch 2006 in the transponder circuitry 100 of FIGS. 1 and 2. The switch circuit 2000 in one example uses the same signal I_{chg} (or $k \cdot I_{chg}$) that is used for the demodulator in order to control the switch 2006 between VCL (shown as vddsw_3p3v) and a battery supply voltage vdd_3p3v. In this example, a default state of the switch is closed, so that vbat_3p3v can supply vddsw_3p3v via the internal voltage vdd_3p3v. When vddsw_3p3v is greater than vdd_3p3v or the LF field is charging vddsw_3p3v, then the switch 2006 is opened by the comparator 2004 and the AND gate 2002.

The above examples are merely illustrative of several possible embodiments of various aspects of the present disclosure, wherein equivalent alterations and/or modifications will occur to others skilled in the art upon reading and understanding this specification and the annexed drawings. Modifications are possible in the described embodiments, and other embodiments are possible, within the scope of the claims.

13

What is claimed is:

1. An electronic device comprising:
 - a plurality of transponder channel circuits;
 - a plurality of transponder antenna circuits, each coupled to a respective one of the transponder channel circuits; and
 - a shared capacitor circuit including:
 - a variable capacitor device;
 - a switching circuit to selectively connected the variable capacitor device to a selected one of the transponder channel circuits; and
 - a control circuit to control the variable capacitor device to provide a selected capacitance.
2. The electronic device of claim 1, wherein:
 - the variable capacitor device includes a plurality of capacitors;
 - the control circuit includes a plurality of switches, each switch being individually controllable and coupled to a respective one of the capacitors, and wherein the control circuit is configured to control selected ones of the switches to a closed state; and
 - the respective capacitor coupled to each of the selected ones of the switches is electrically connected to an input of the selected one of the transponder channel circuits.
3. The electronic device of claim 2, wherein each of the capacitors has a different capacitance value.
4. The electronic device of claim 3, wherein the capacitance values of the capacitors are binary weighted capacitance values.
5. The electronic device of claim 2, wherein the capacitors coupled to the selected ones of the switches collectively provide the selected capacitance.
6. The electronic device of claim 2, wherein each switch is a complementary pass gate that includes an NMOS transistor and a PMOS transistor.
7. The electronic device of claim 1, wherein the control circuit is configured control the variable capacitor device so that the selected capacitance changes between a first capacitance and a second capacitance to transmit data using the transponder antenna circuit coupled to the selected one of the transponder channel circuits.
8. The electronic device of claim 1, wherein the transmitted data is transmitted by the transponder antenna circuit coupled to the selected one of the transponder channel circuits using frequency shift keying (FSK).
9. The electronic device of claim 1, wherein the plurality of transponder antenna circuits include three transponder antenna circuits, each of the three transponder antenna circuits having a respective antenna, the antenna of each one of the three transponder antenna circuits being arranged in an orientation different from the antenna of each other one of the three transponder antenna circuits.
10. The electronic device of claim 9, wherein the respective antennas of the three transponder antenna circuits are arranged as three mutually orthogonal antennas.
11. The electronic device of claim 1, wherein the electronic device is a key fob device.
12. An electronic key fob device comprising:
 - a first transponder channel circuit;
 - a first antenna coupled to the first transponder channel circuit;
 - a second transponder channel circuit;
 - a second antenna coupled to the first transponder channel circuit; and

14

- a shared capacitor circuit including:
 - a variable capacitor device;
 - a switching circuit to selectively connected the variable capacitor device to an input of a selected one of at least the first and second transponder channel circuits; and
 - a control circuit to control the variable capacitor device to provide a selected capacitance.
- 13. The electronic key fob device of claim 12, wherein:
 - the variable capacitor device includes a plurality of capacitors;
 - the control circuit includes a plurality of switches, each switch being individually controllable and coupled to a respective one of the capacitors, and wherein the control circuit is configured to control selected ones of the switches to a closed state; and
 - the respective capacitor coupled to each of the selected ones of the switches is electrically connected to the input of the selected one of at least the first and second transponder channel circuits to collectively provide the selected capacitance.
- 14. The electronic key fob device of claim 13, wherein each of the capacitors has a different capacitance value.
- 15. An integrated circuit comprising:
 - a plurality of transponder channel circuits;
 - a plurality of transponder antenna circuits, each coupled to a respective one of the transponder channel circuits; and
 - a shared capacitor circuit including:
 - a variable capacitor device including a plurality of capacitors;
 - a switching circuit to selectively connected the variable capacitor device to a selected one of the transponder channel circuits; and
 - a control circuit to control the variable capacitor device to provide a selected capacitance, the control circuit including a plurality of switches, each switch being individually controllable and coupled to a respective one of the capacitors, and wherein the control circuit is configured to control selected ones of the switches to a closed state, and the respective capacitor coupled to each of the selected ones of the switches is electrically connected to an input of the selected one of the transponder channel circuits.
- 16. The integrated circuit of claim 15, wherein each of the capacitors has a different capacitance value.
- 17. The integrated circuit of claim 16, wherein the capacitance values of the capacitors are binary weighted capacitance values.
- 18. The integrated circuit of claim 17, wherein the plurality of capacitors includes first, second, third, fourth, fifth, sixth, seventh, and eighth capacitors, and wherein:
 - the first capacitor has a first capacitance value;
 - the second capacitor has a second capacitance value that is twice the first capacitance value;
 - the third capacitor has a third capacitance value that is twice the second capacitance value;
 - the fourth capacitor has a fourth capacitance value that is twice the third capacitance value;
 - the fifth capacitor has a fifth capacitance value that is twice the fourth capacitance value;
 - the sixth capacitor has a sixth capacitance value that is twice the fifth capacitance value;
 - the seventh capacitor has a seventh capacitance value that is twice the sixth capacitance value; and
 - the eighth capacitor has an eighth capacitance value that is twice the seventh capacitance value.